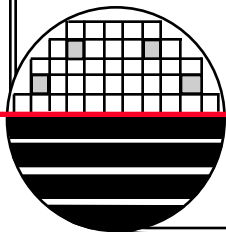


**ROCHESTER INSTITUTE OF TECHNOLOGY  
MICROELECTRONIC ENGINEERING**

**SEMS of MEMS Devices**

**Dr. Lynn Fuller**

**Motorola Professor  
Microelectronic Engineering  
Rochester Institute of Technology  
82 Lomb Memorial Drive  
Rochester, NY 14623-5604  
Tel (585) 475-2035  
Fax (585) 475-5041  
[LFFEEE@rit.edu](mailto:LFFEEE@rit.edu)  
<http://www.microe.rit.edu>**



*OUTLINE*

Introduction  
Scanning Electron Microscope  
SEM Micrographs of  
    Microphone  
    Accelerometers  
    Mirrors  
    Electrodes  
    Pillars and Posts  
    KOH Etched Holes in Single Crystal Silicon  
    Micromotors and Gears  
    Steam Engine  
References  
Homework

*LEO EVO 50*

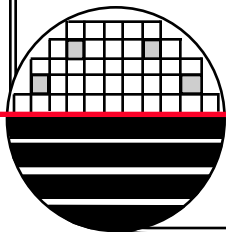


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Microelectronic Engineering*

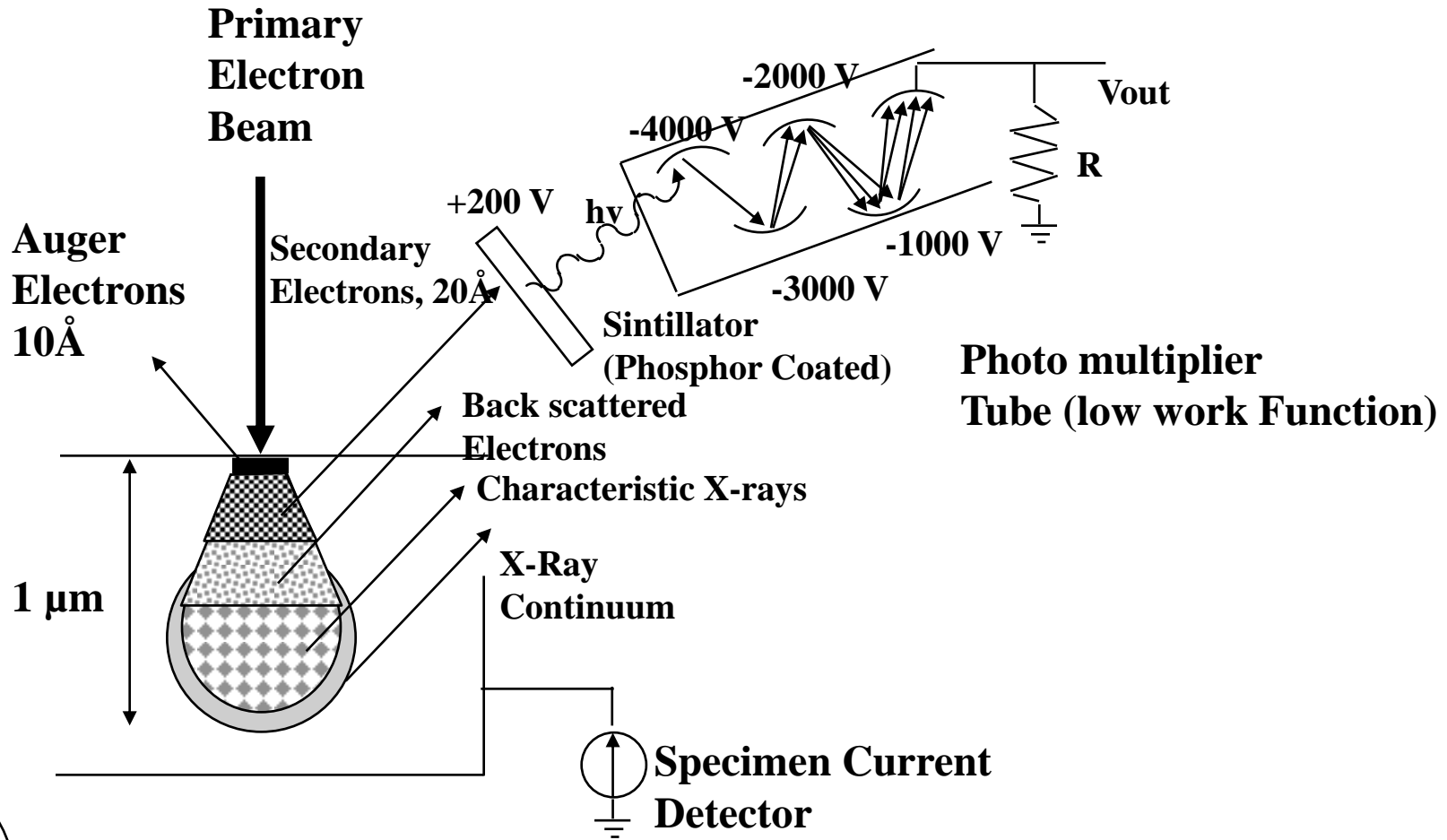
*AMRAY 1830 1 & 2*



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Microelectronic Engineering*



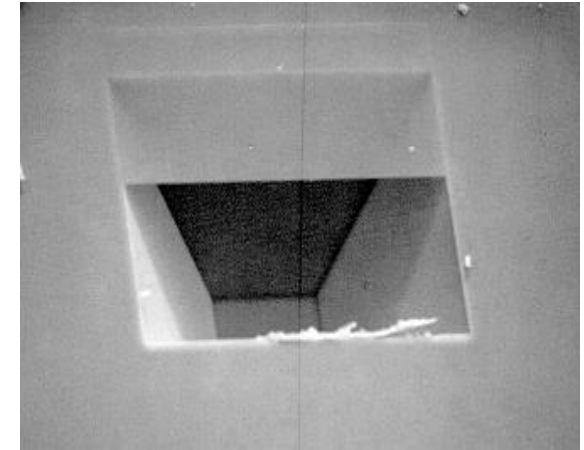
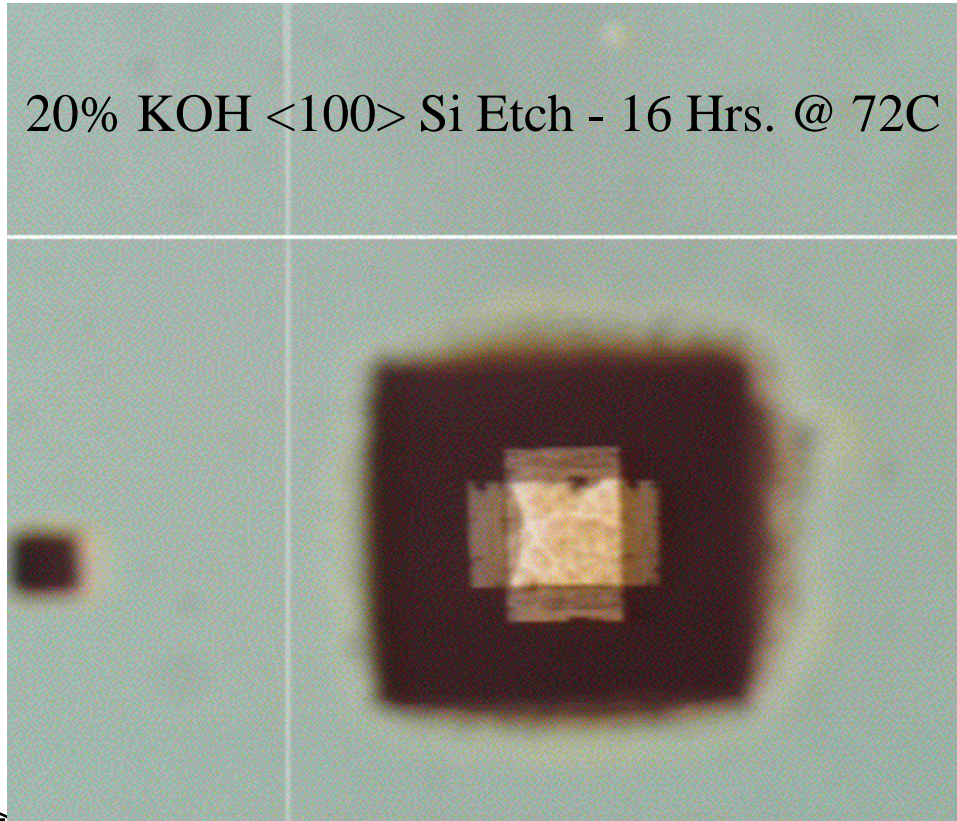
# SCANNING ELECTRON MICROSCOPE (SEM)



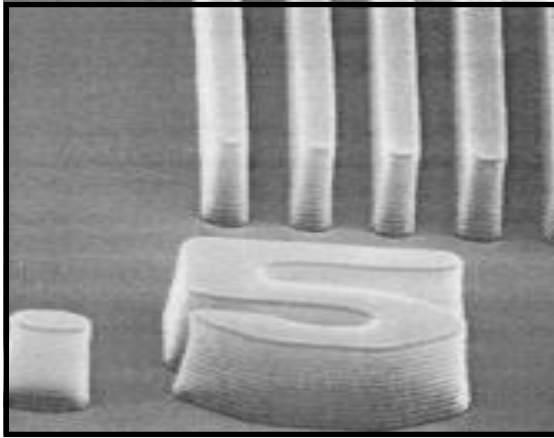
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Microelectronic Engineering

## *ILLUSTRATION OF LARGE DEPTH OF FOCUS*

Optical picture focused on bottom of etch pit



SEM Gives Large Depth  
of Focus and High  
Resolution

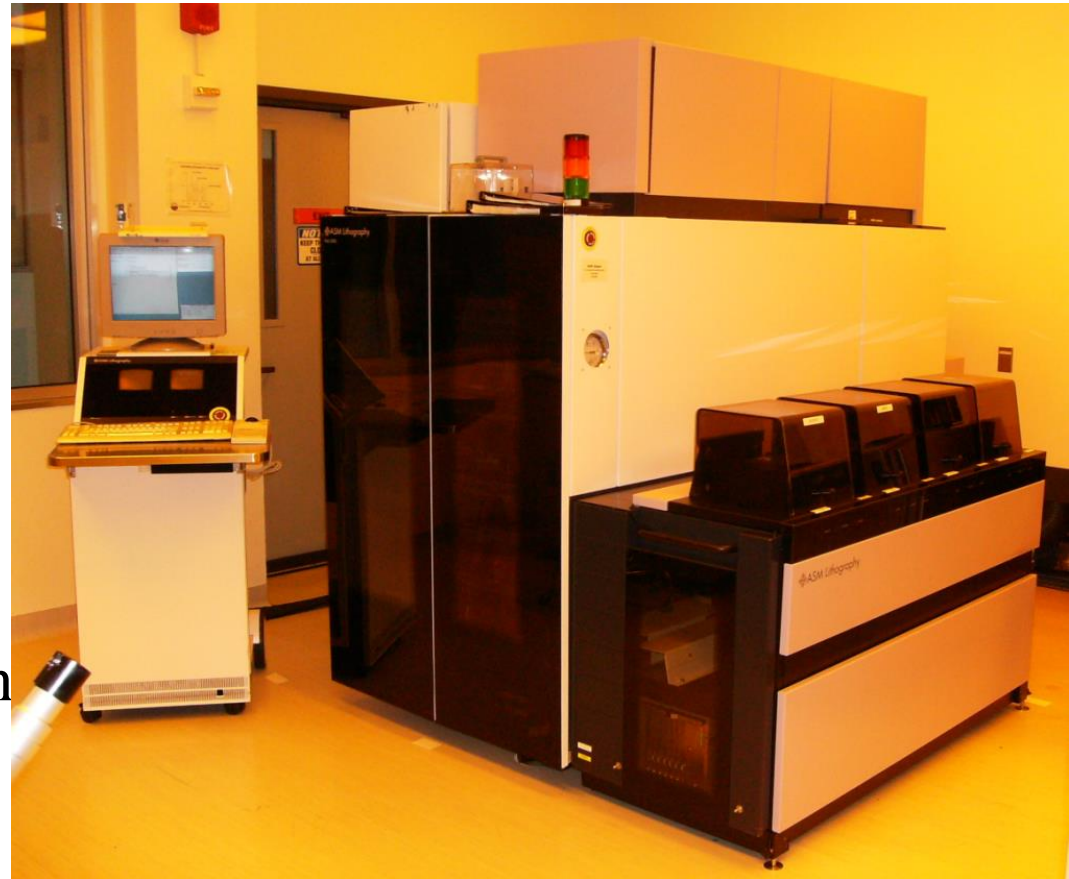
*ASML 5500/200*

NA = 0.48 to 0.60 variable  
 $\sigma = 0.35$  to 0.85 variable  
 With Variable Kohler, or  
 Variable Annular illumination  
 Resolution =  $K_1 \lambda / NA$

=  $\sim 0.35 \mu\text{m}$

for NA=0.6,  $\sigma = 0.85$

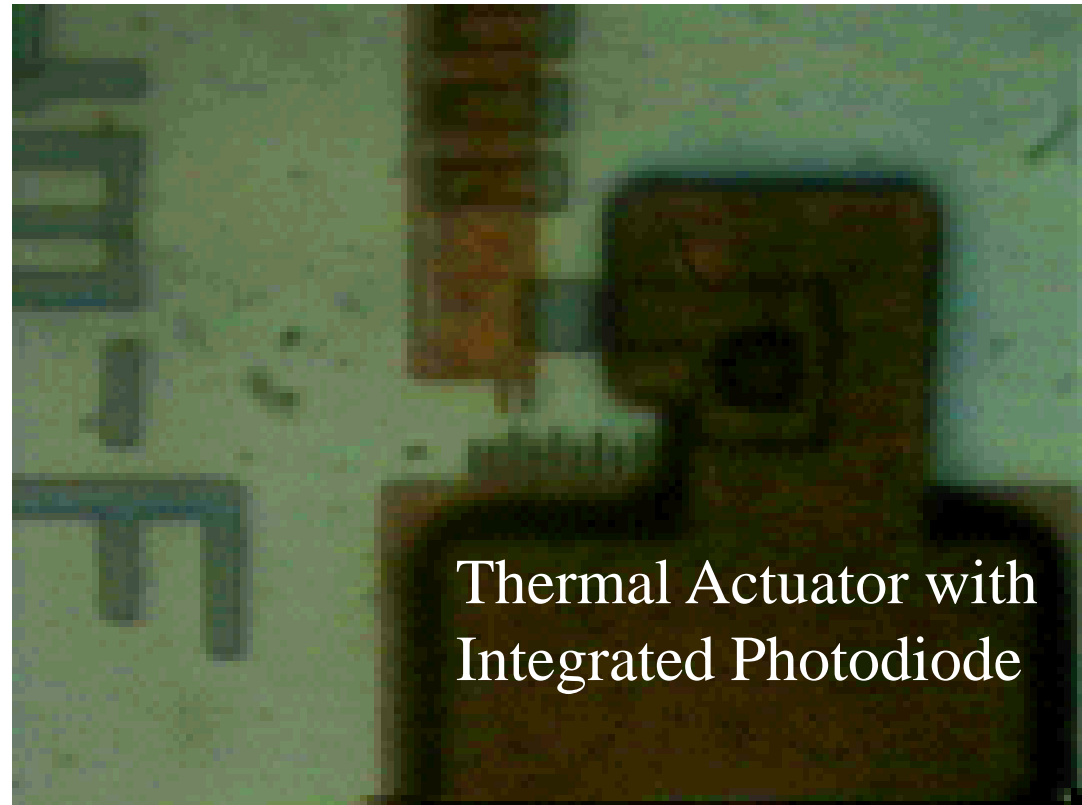
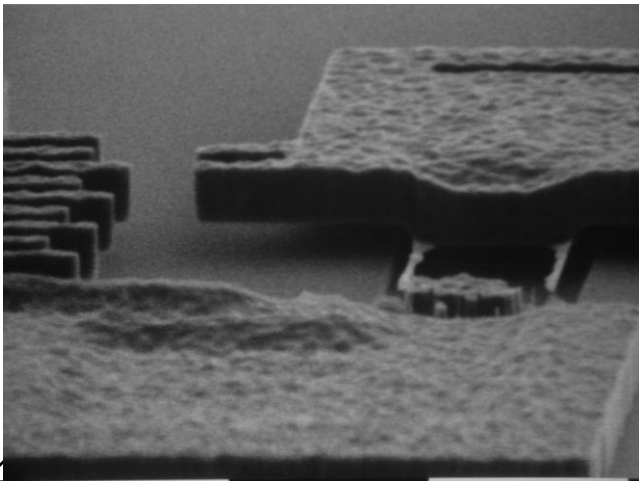
Depth of Focus =  $k_2 \lambda / (NA)^2$   
 =>  $1.0 \mu\text{m}$  for NA = 0.6



i-Line Stepper  $\lambda = 365 \text{ nm}$   
 22 x 27 mm Field Size

# INTEGRATION OF PHOTODIODE AND MEMS

December 2001  
Kevin Munger. joined  
IBM Burlington, VT

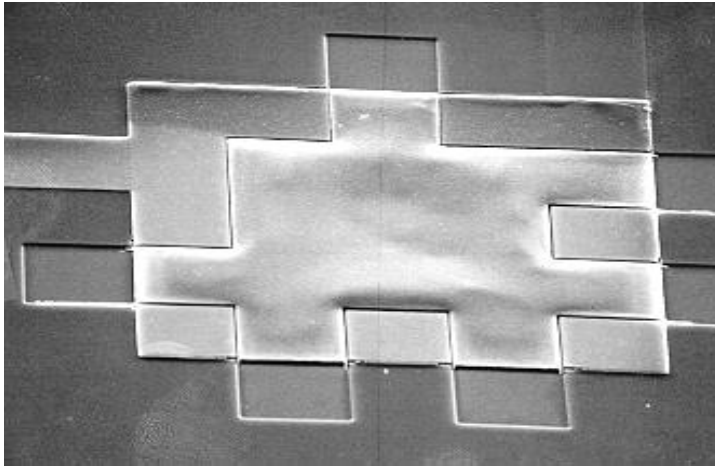


Maximum Deflection  $9 \mu\text{m}$  at  $30 \mu\text{w}$   
162,000 cycles, 6 msec.,

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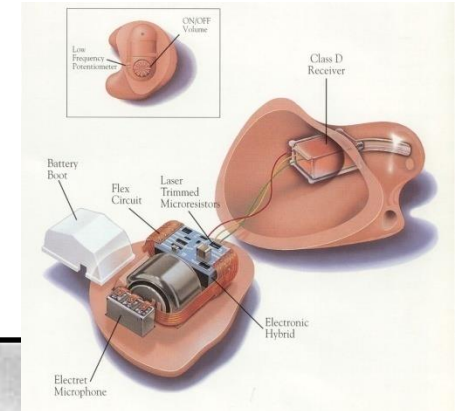
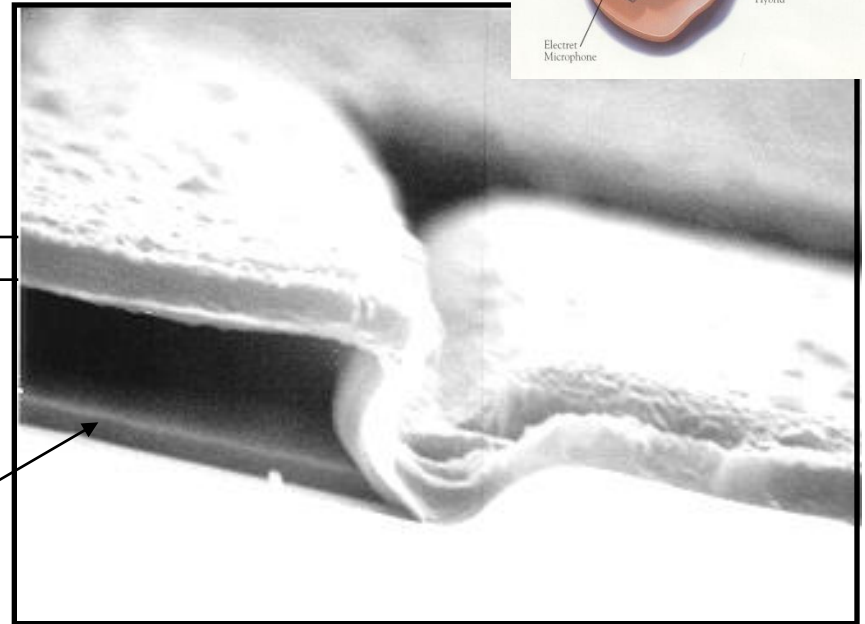
# ALUMINUM DIAPHRAGM CAPACITIVE MICROPHONE



1  $\mu\text{m}$  Aluminum

**Jon Stephan, 1995, now at  
Intel Corporation  
Folsom, CA**

2.0  $\mu\text{m}$  Gap



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Microelectronic Engineering*

# ACCELEROMETER

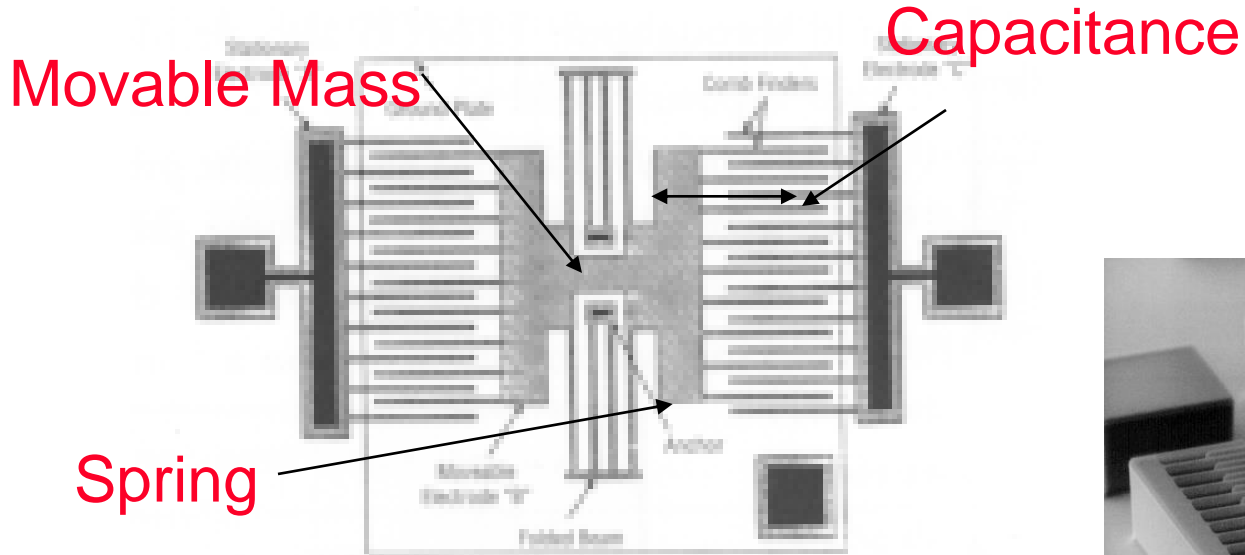
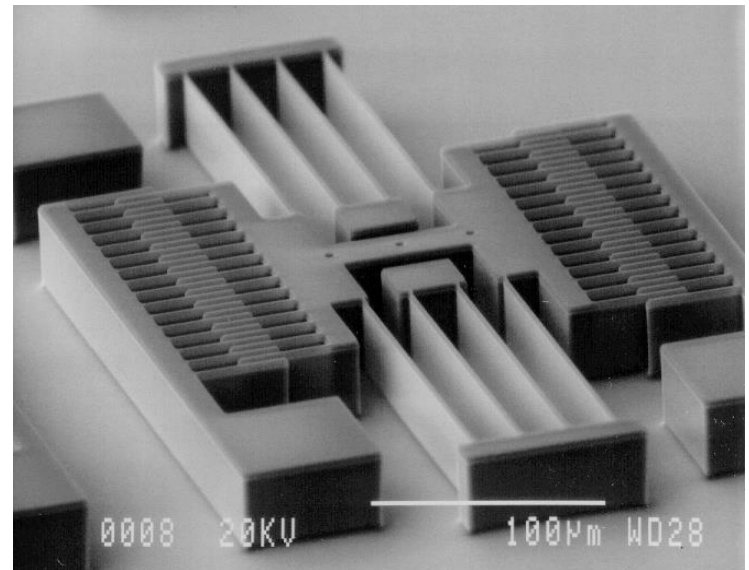
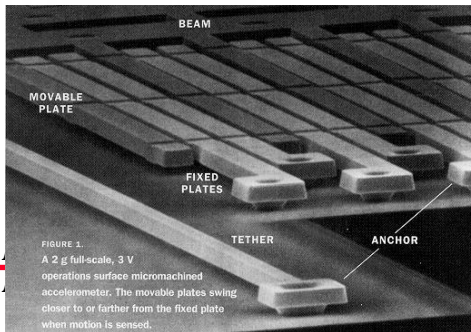


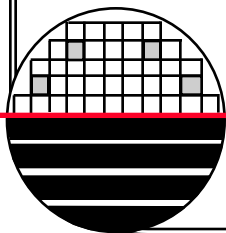
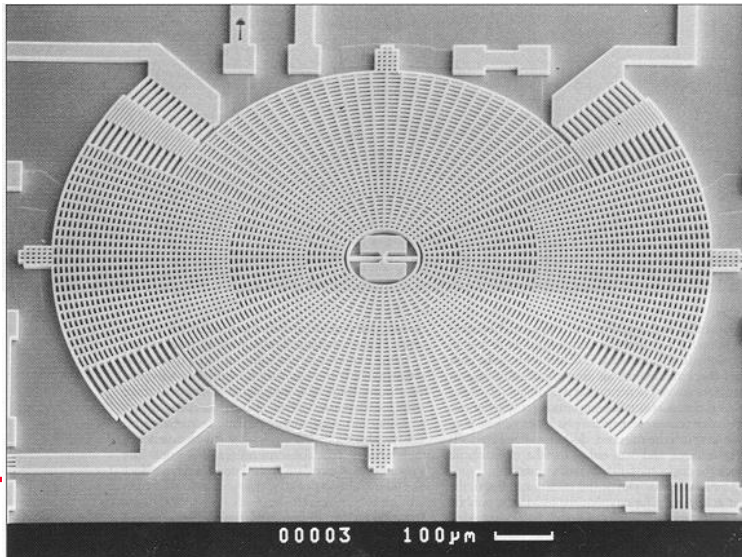
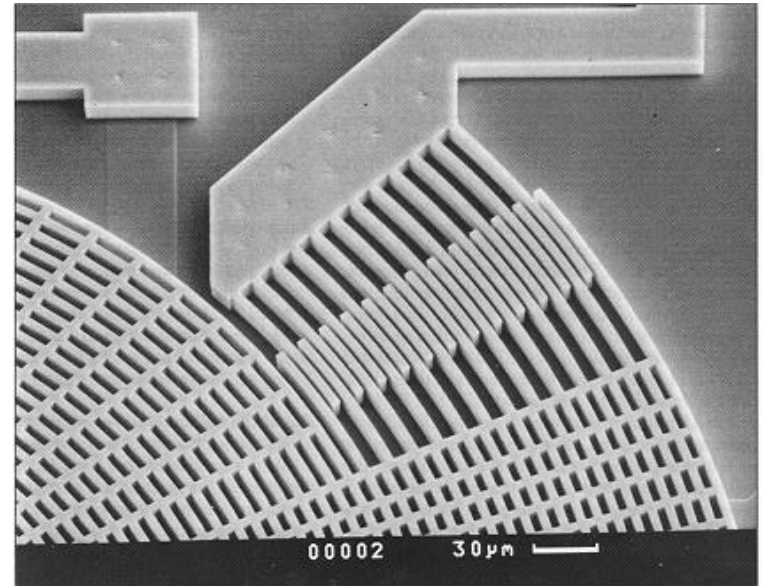
Figure 1: Capacitive Accelerometer Structure



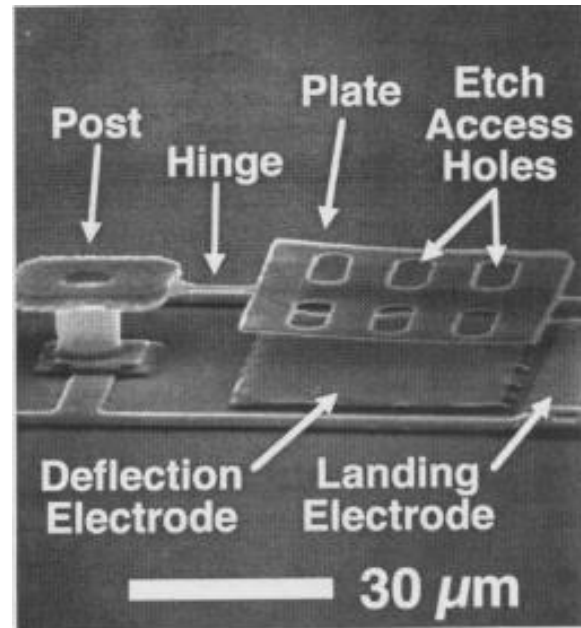
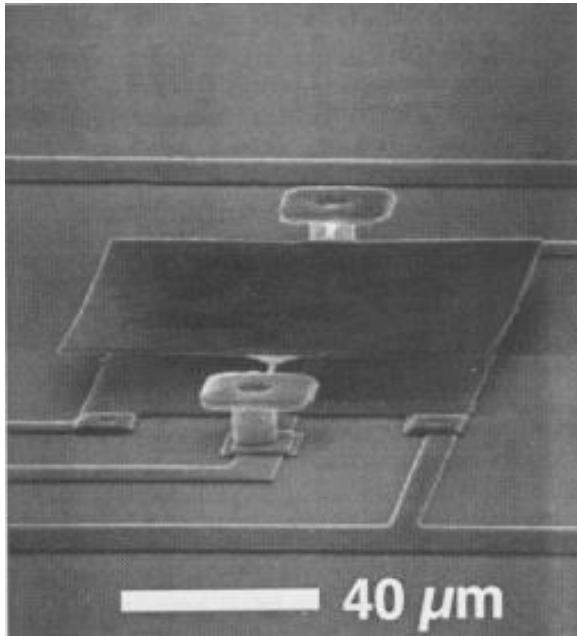
**Bulk Silicon Accelerometer  
(Courtesy of MCNC)**



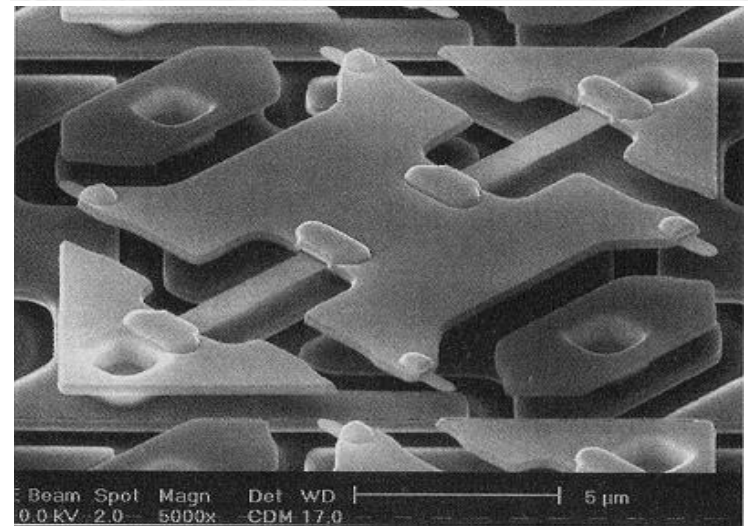
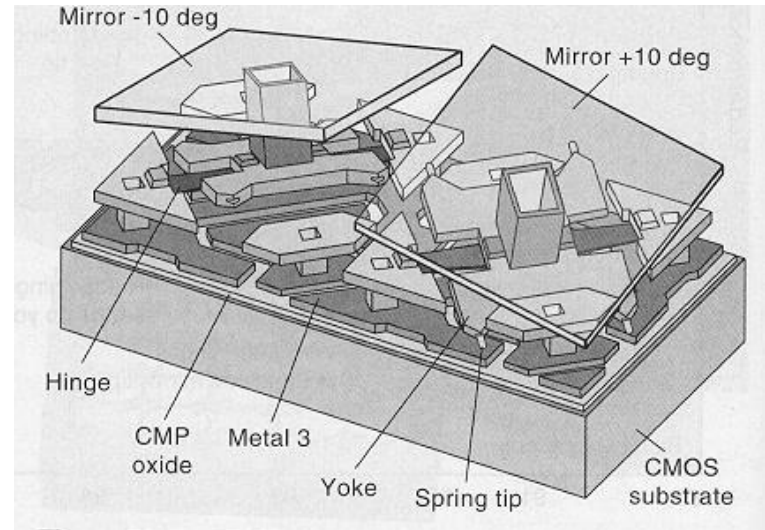
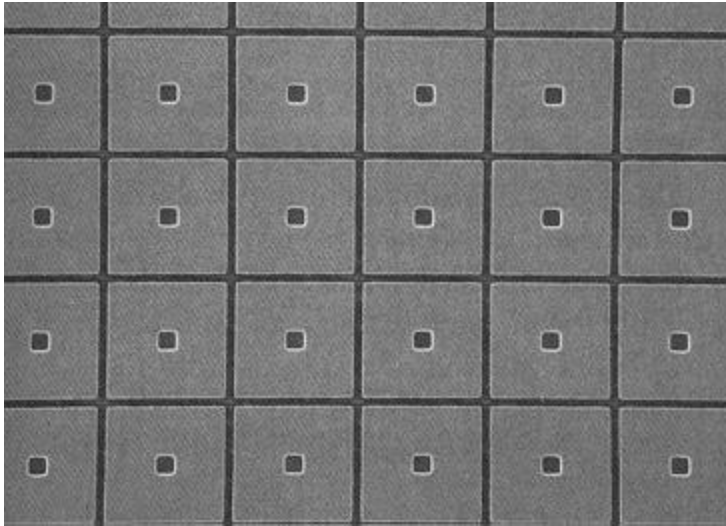
*ANGULAR RATE MEASUREMENT*



# MIRRORS

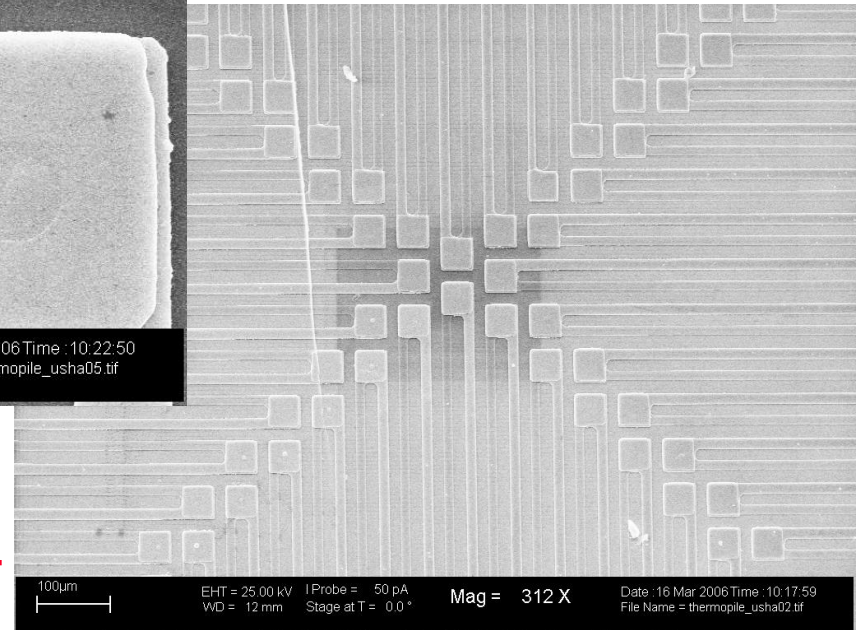
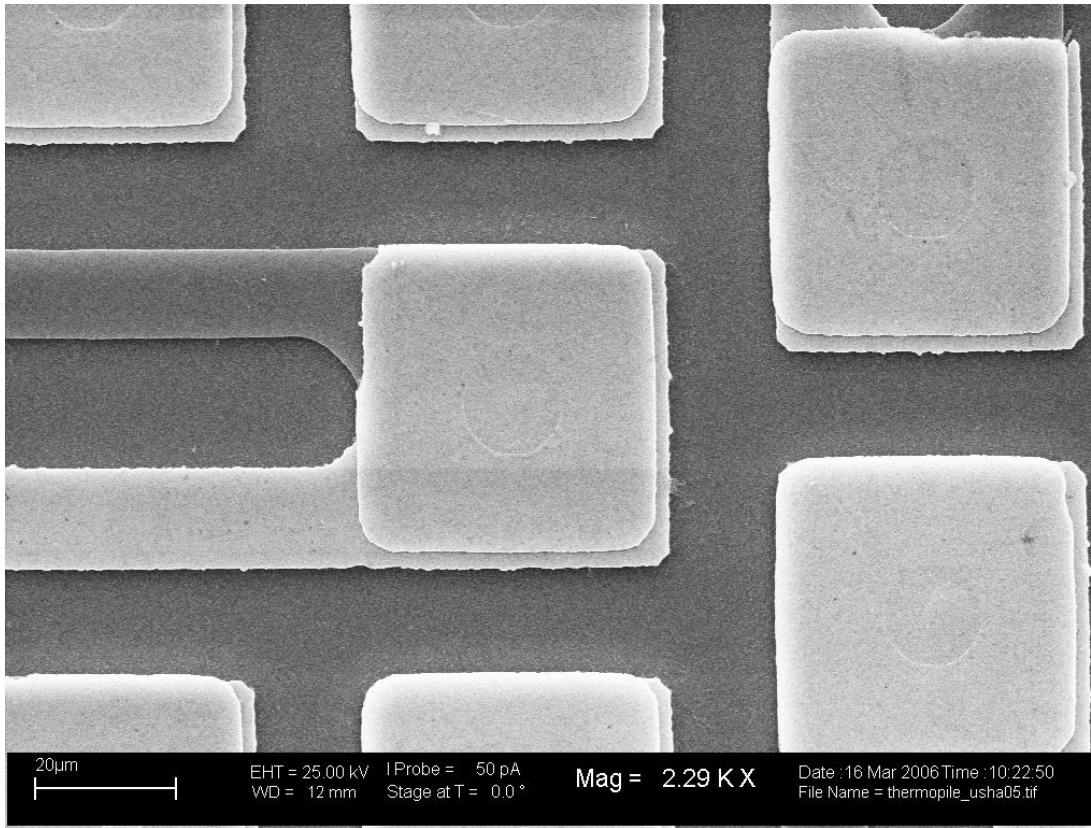


# MIRRORS



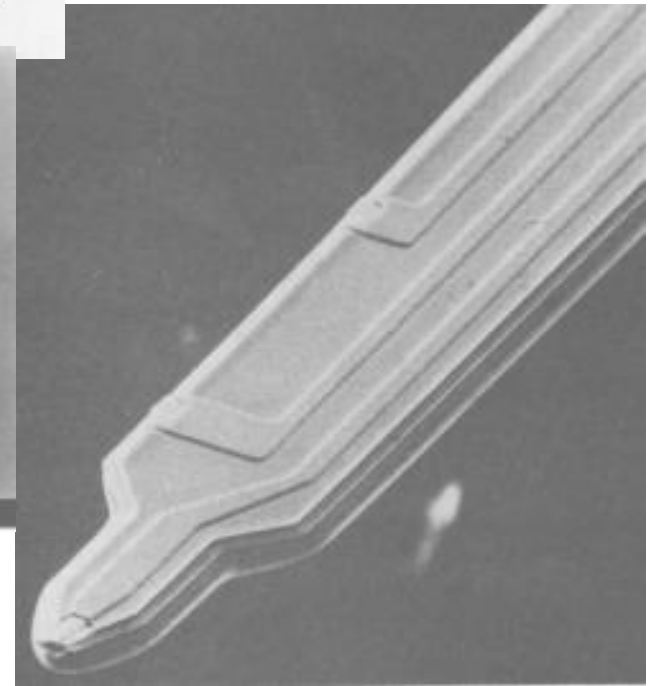
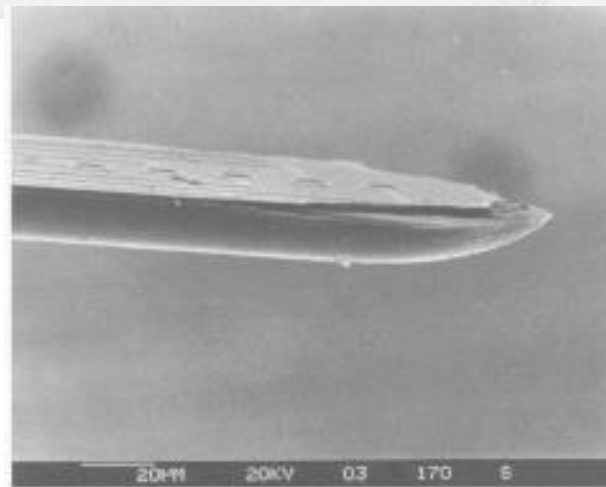
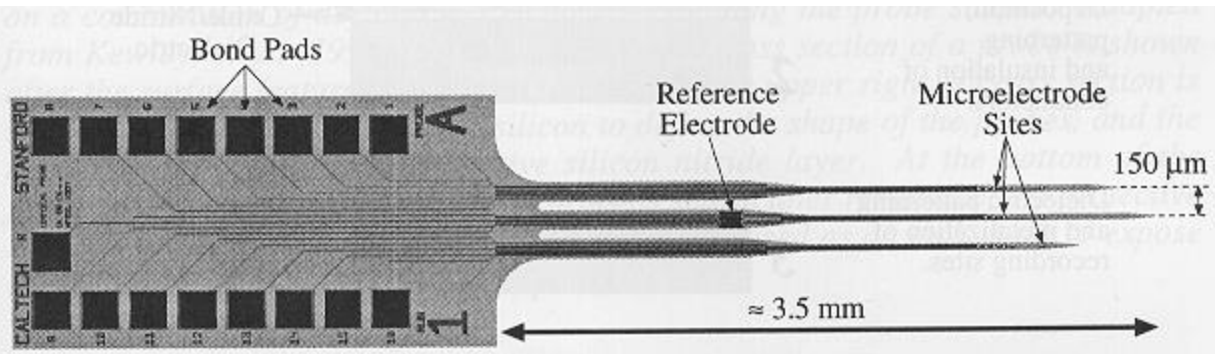
**THERMOPILE**

2006



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*Microelectronic Engineering*

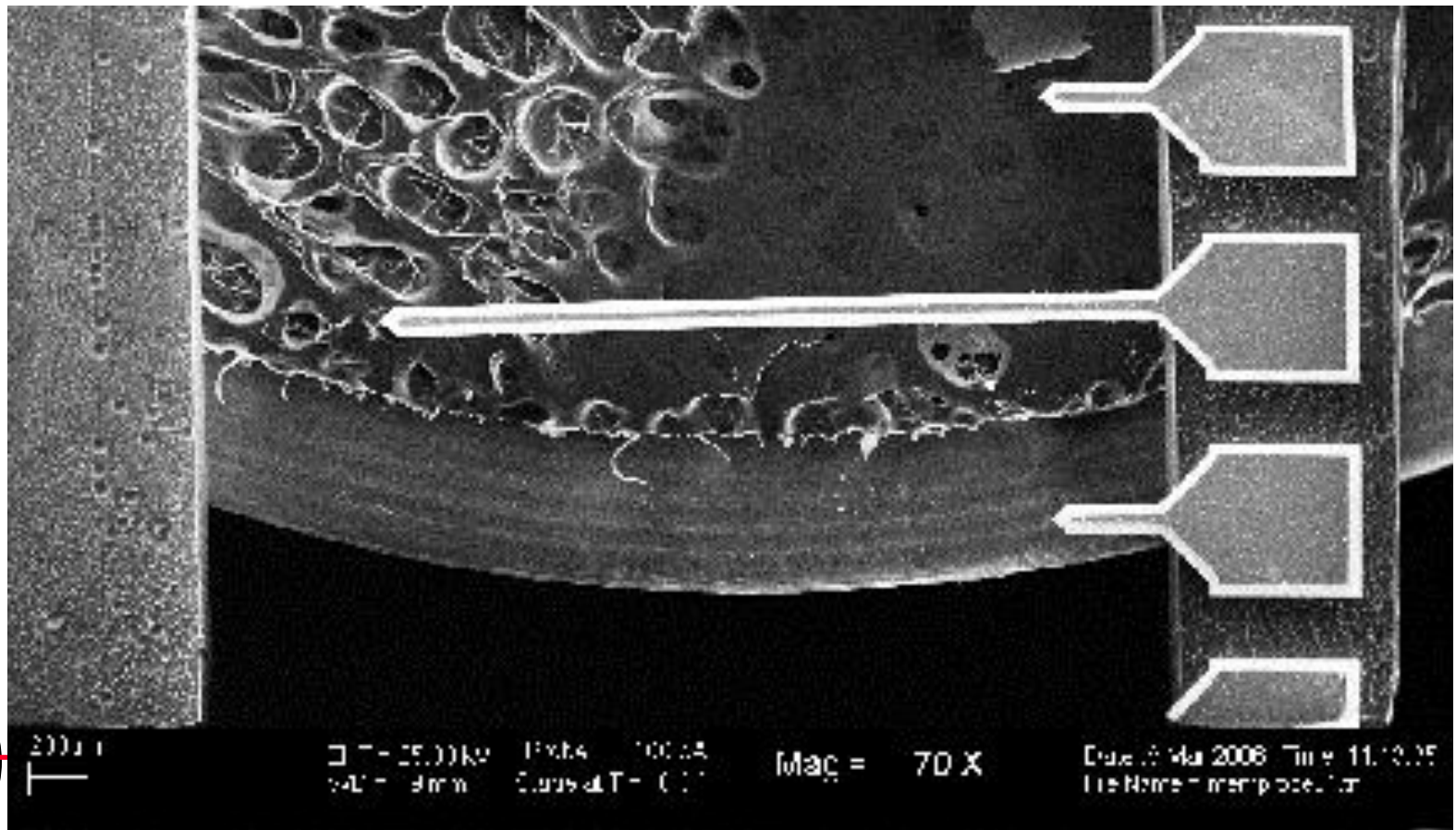
***SENSING ELECTRODES***



***SEM AFTER RELEASE***

The bright white outline is the undercut of the aluminum during plasma etch of the silicon. ~30 $\mu$ m

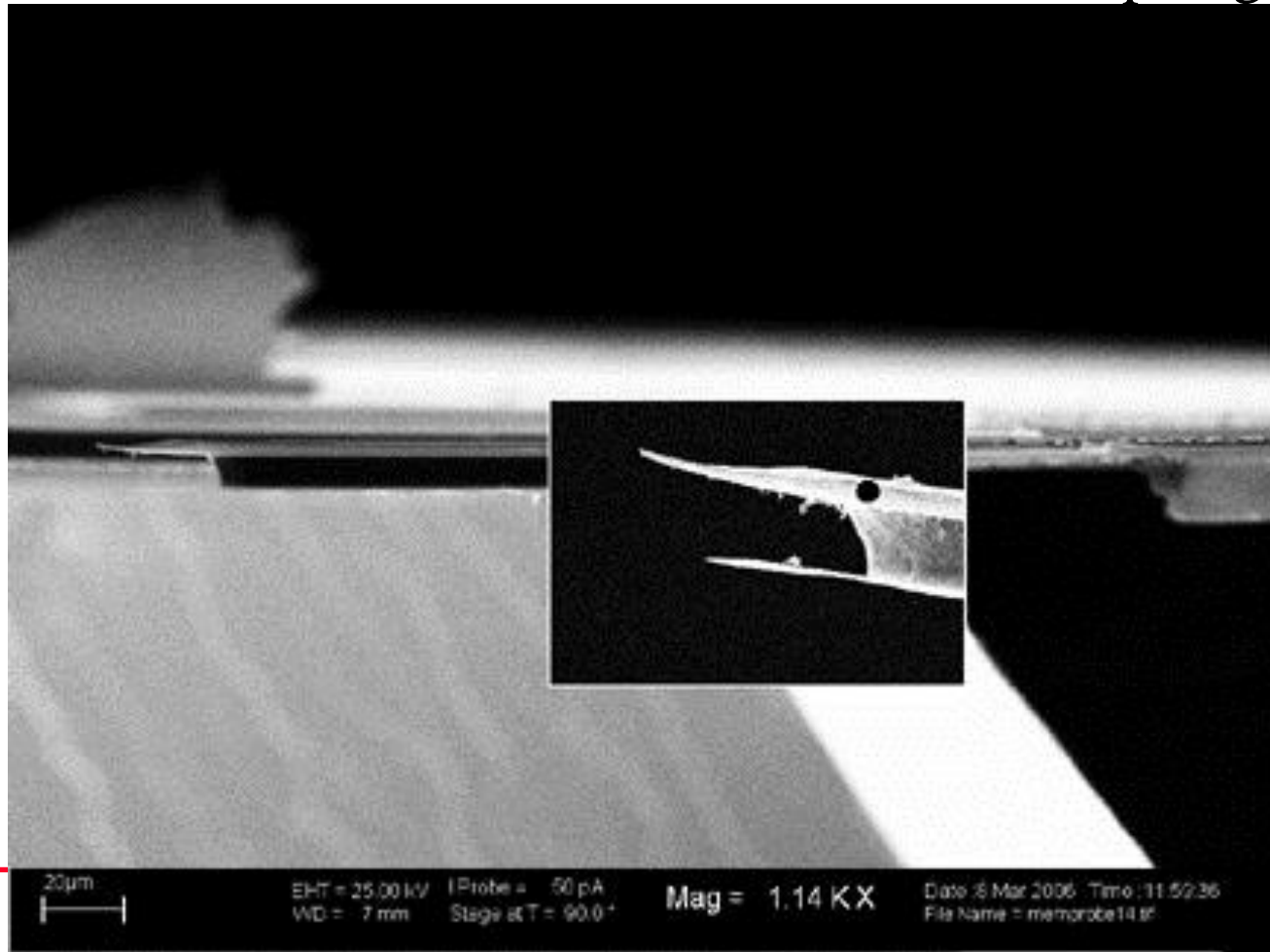
2006





***SEM OF TIP AFTER RELEASE***

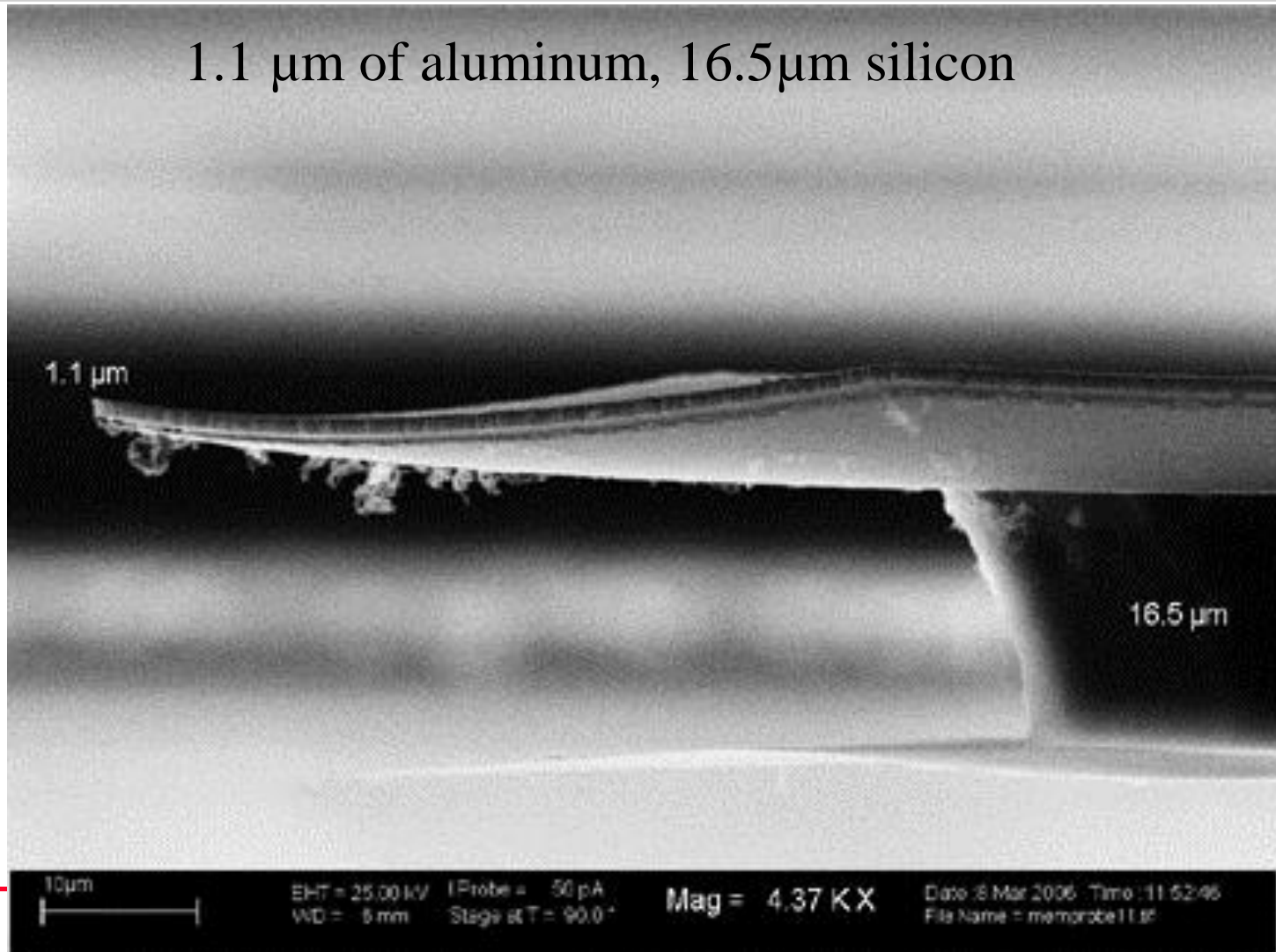
This picture of the tip shows aluminum on top, undercut silicon and thin film of nitride from the bottom of the diaphragm



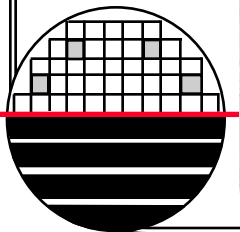
2006

*SEM OF TIP*

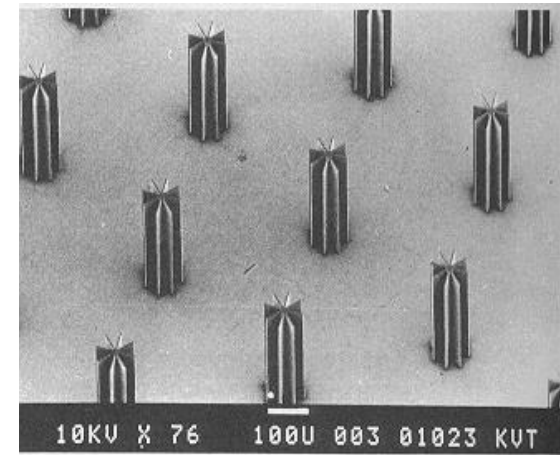
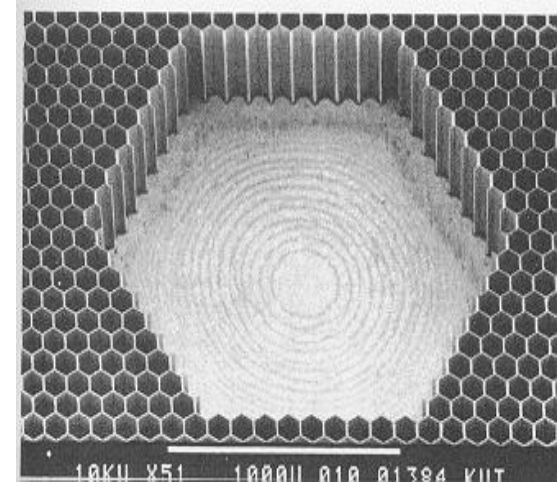
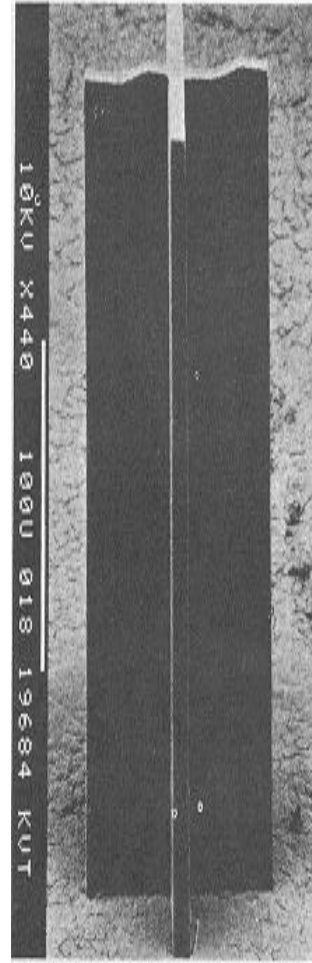
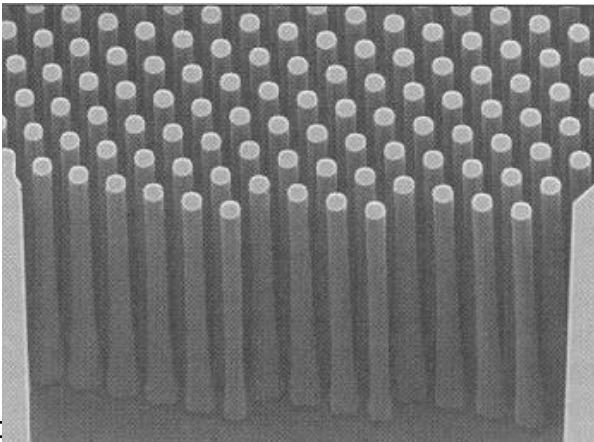
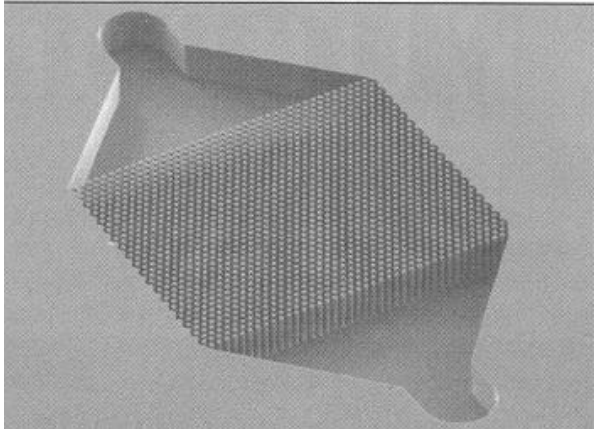
1.1  $\mu\text{m}$  of aluminum, 16.5  $\mu\text{m}$  silicon



2006

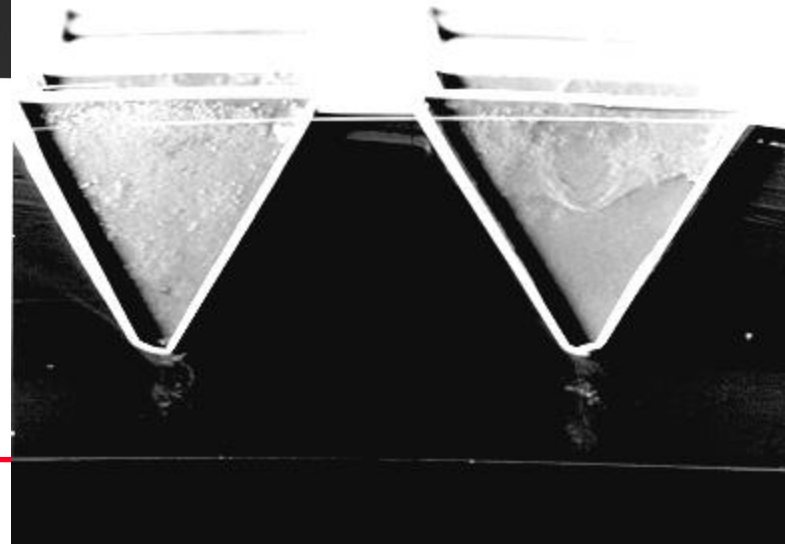
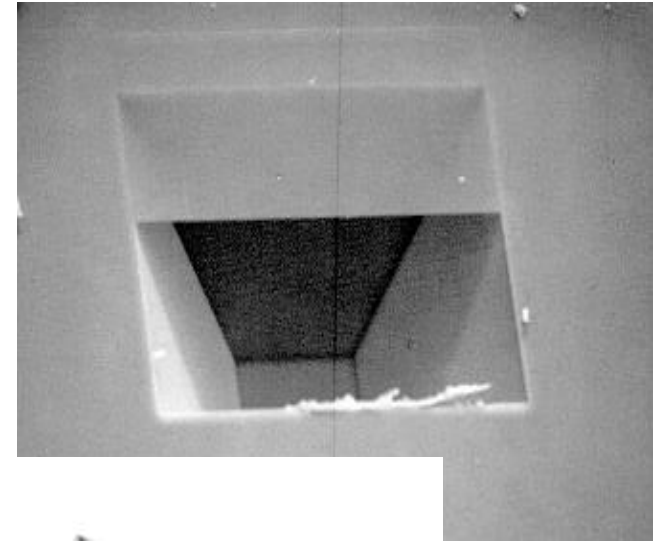
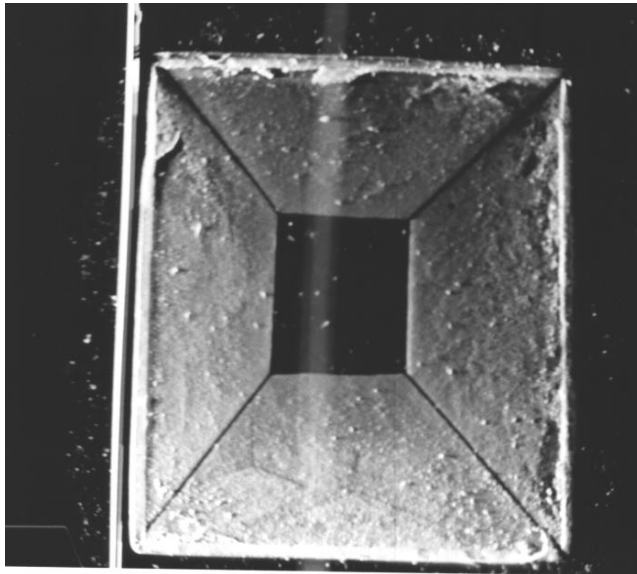


*PILLARS AND POSTS*



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Microelectronic Engineering*

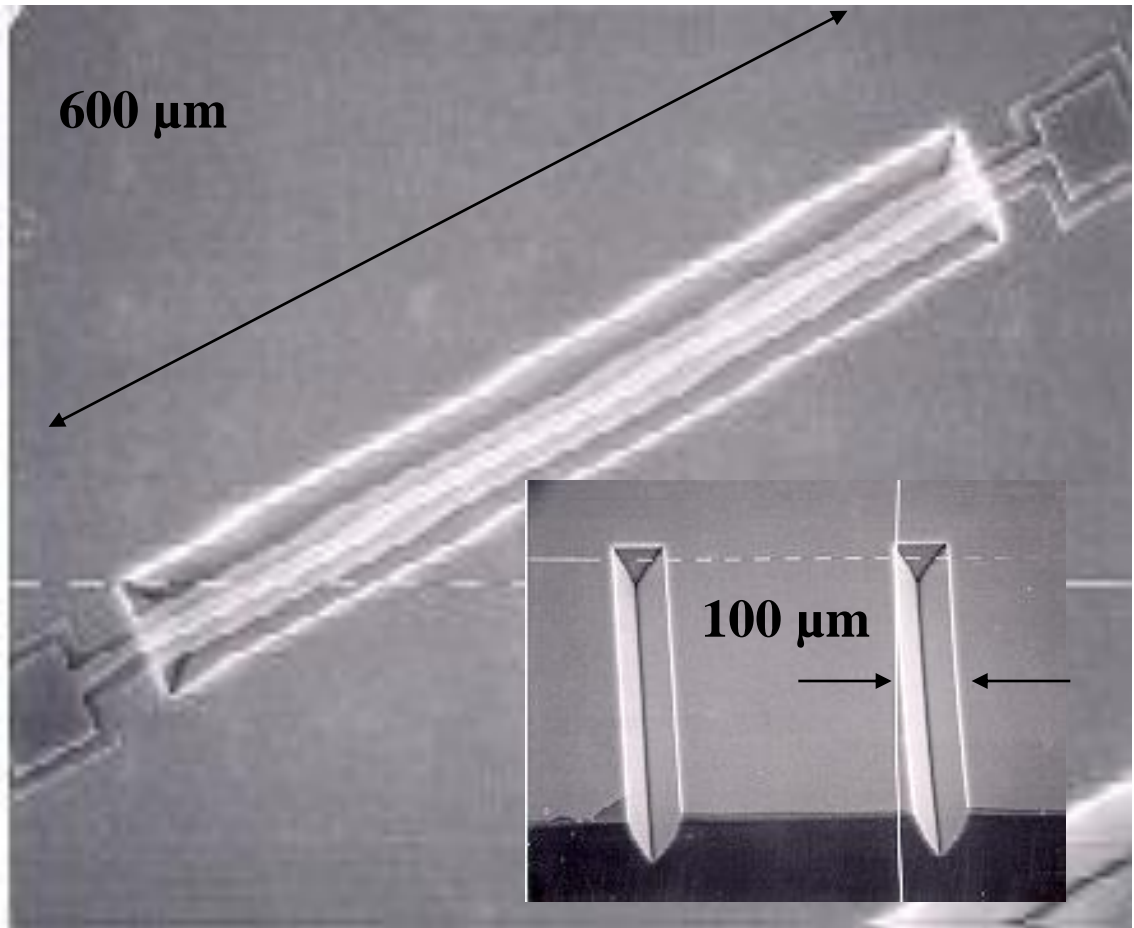
***KOH ETCHED HOLES IN SINGLE CRYSTAL SILICON***



*Rochester Institute of Technology  
Microelectronic Engineering*

***HOT FILAMENT LIGHT SOURCES***

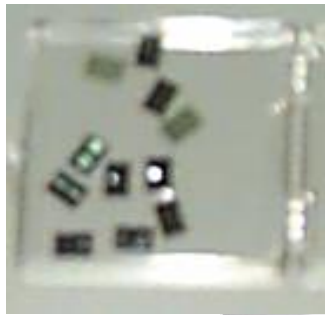
**Dave Borkholder,  
Professor EE at RIT  
Stanford University  
Palo Alto, CA**



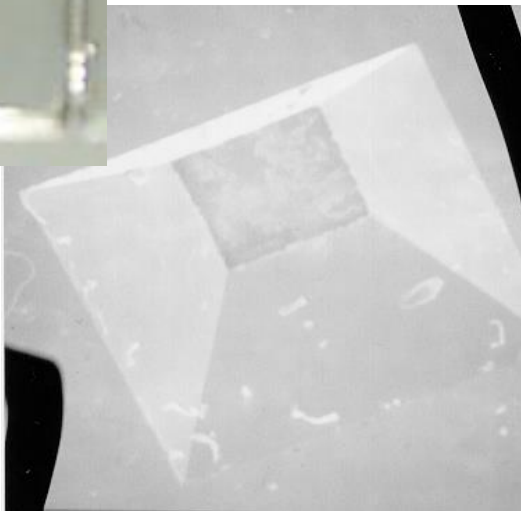
*Rochester Institute of Technology  
Microelectronic Engineering*

## *FLOW PLATES FOR FULE INJECTION*

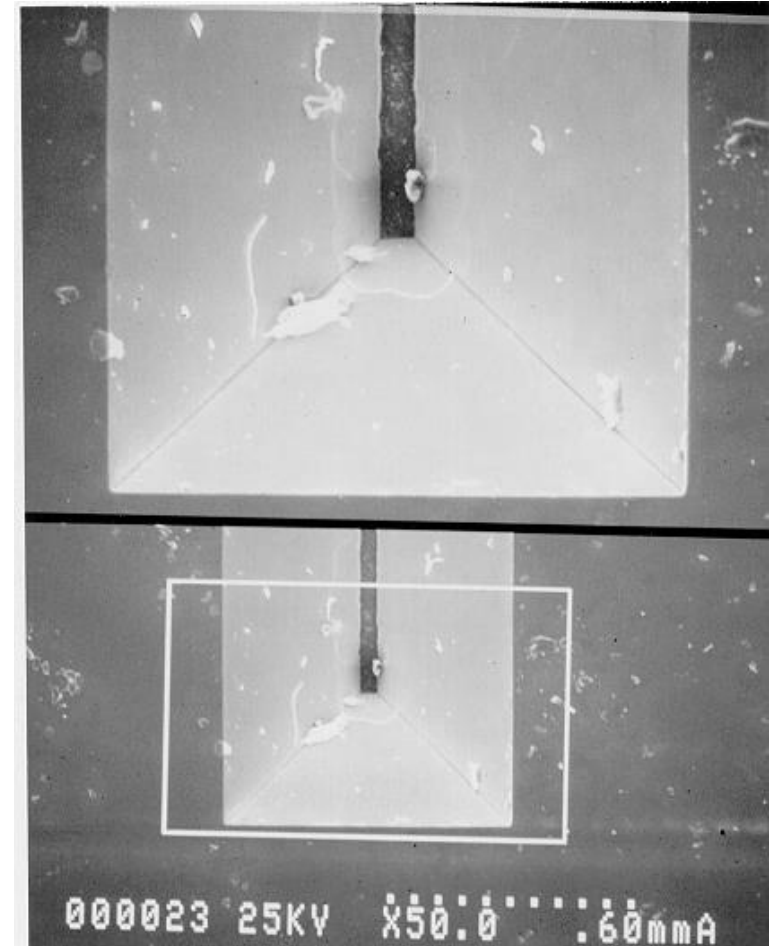
Variety of different size and shape holes etched through 500  $\mu\text{m}$  thick silicon wafer



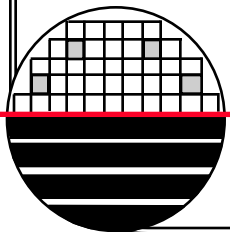
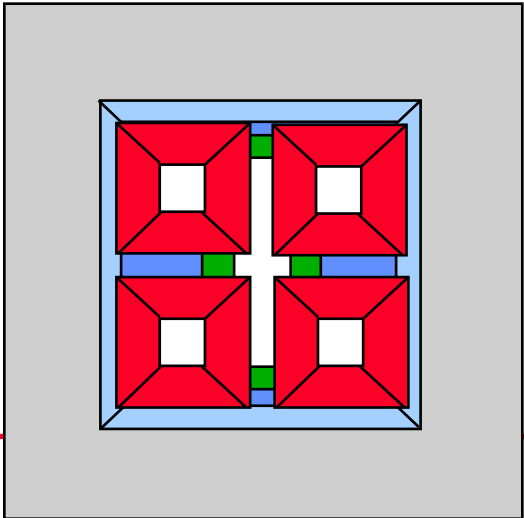
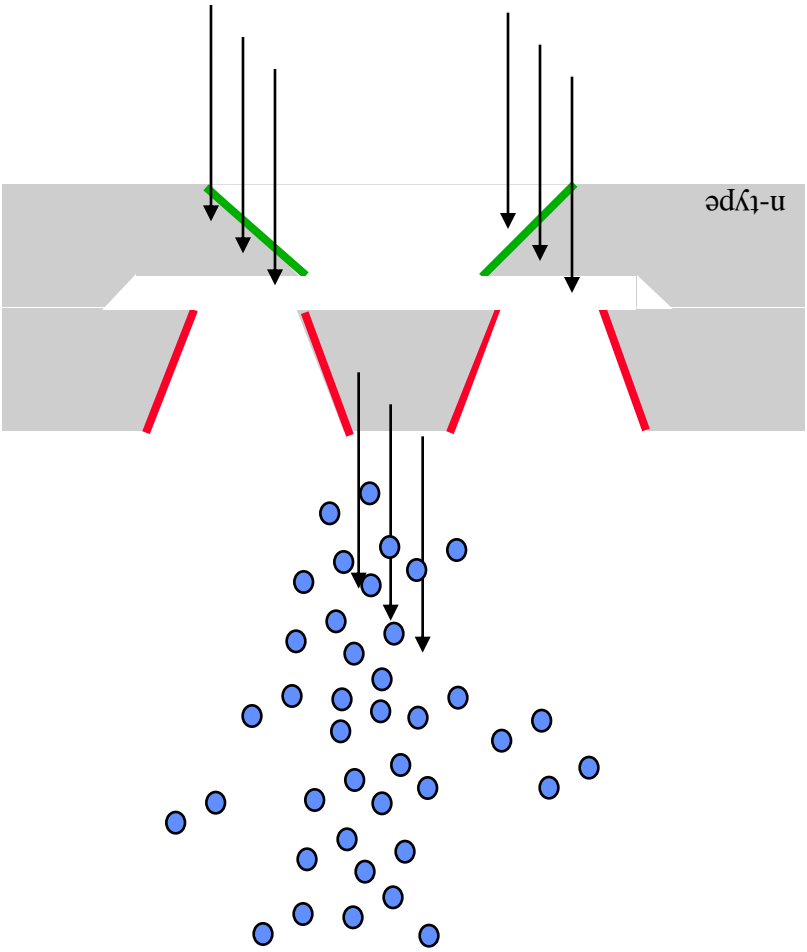
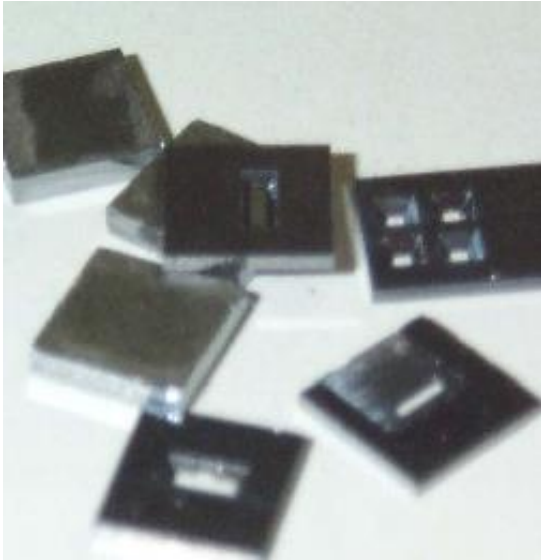
Dr. Risa Robinson  
Delphi Products, Inc.



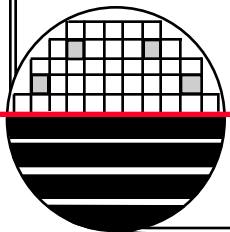
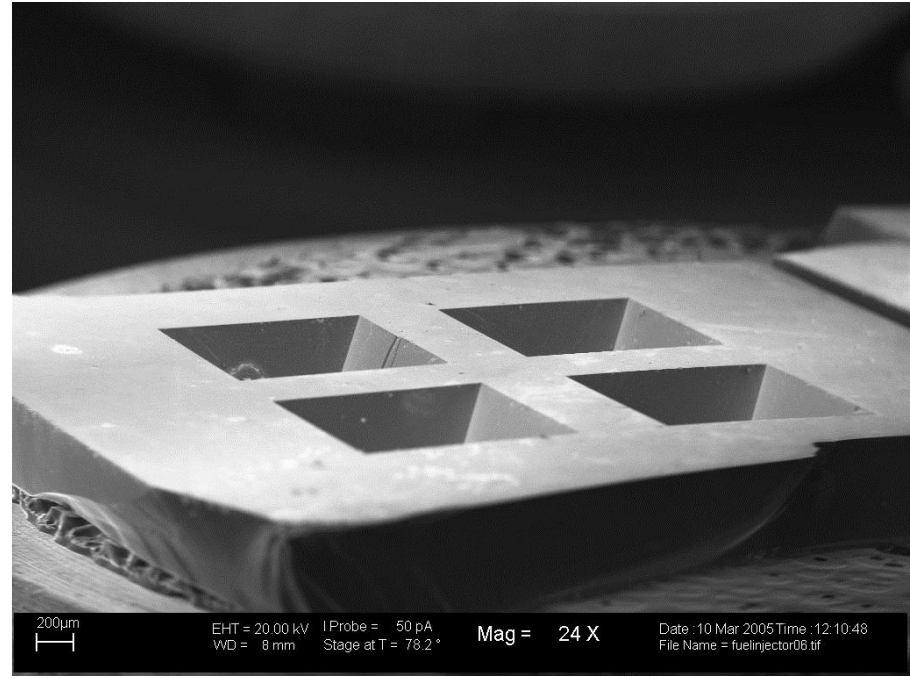
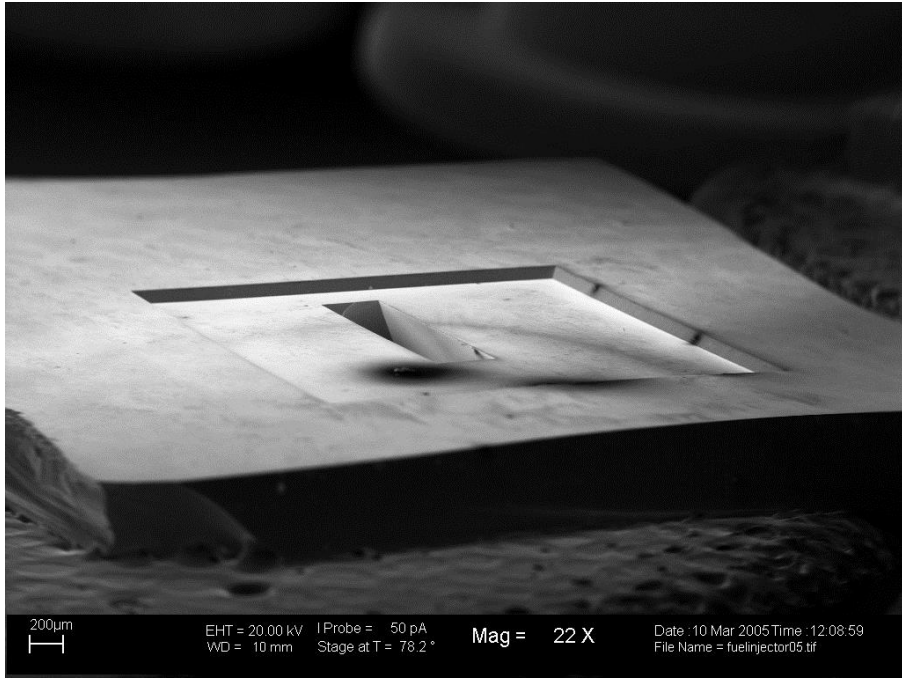
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Microelectronic Engineering*



# FULE INJECTION

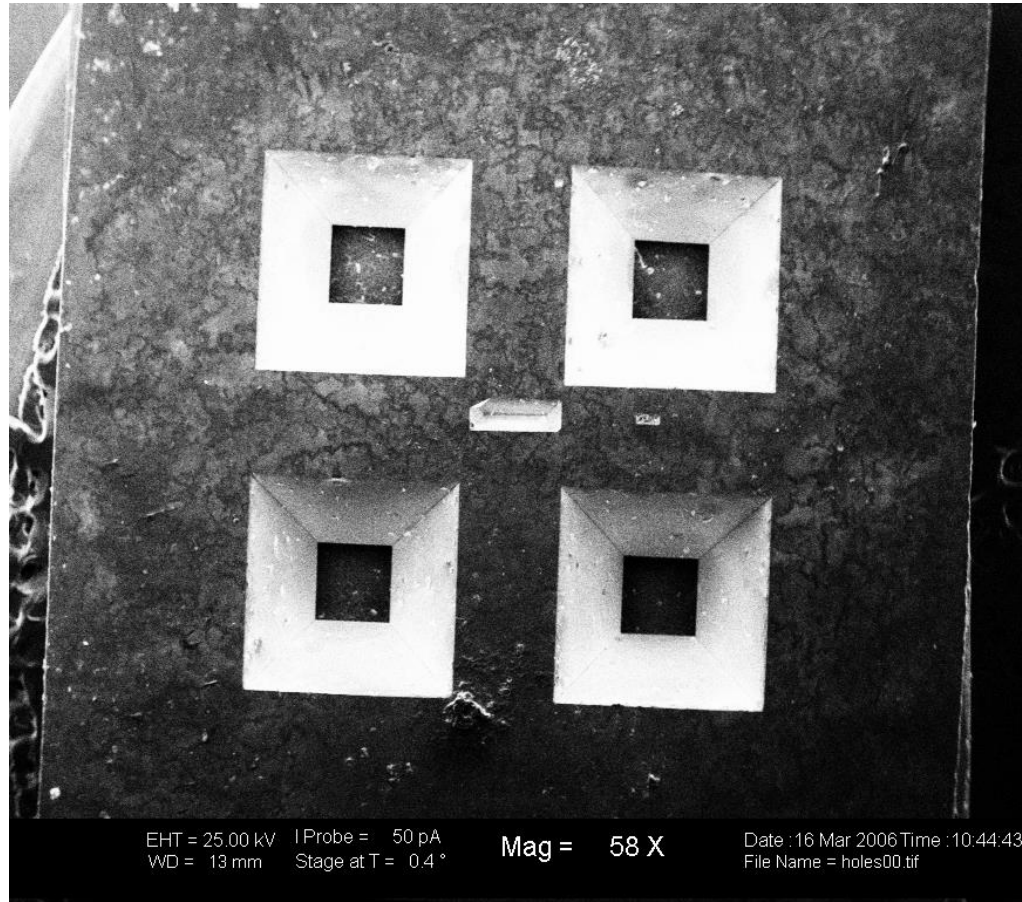


**FULE INJECTOR**

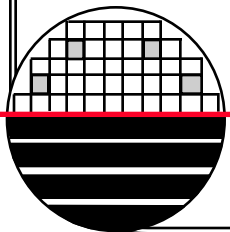
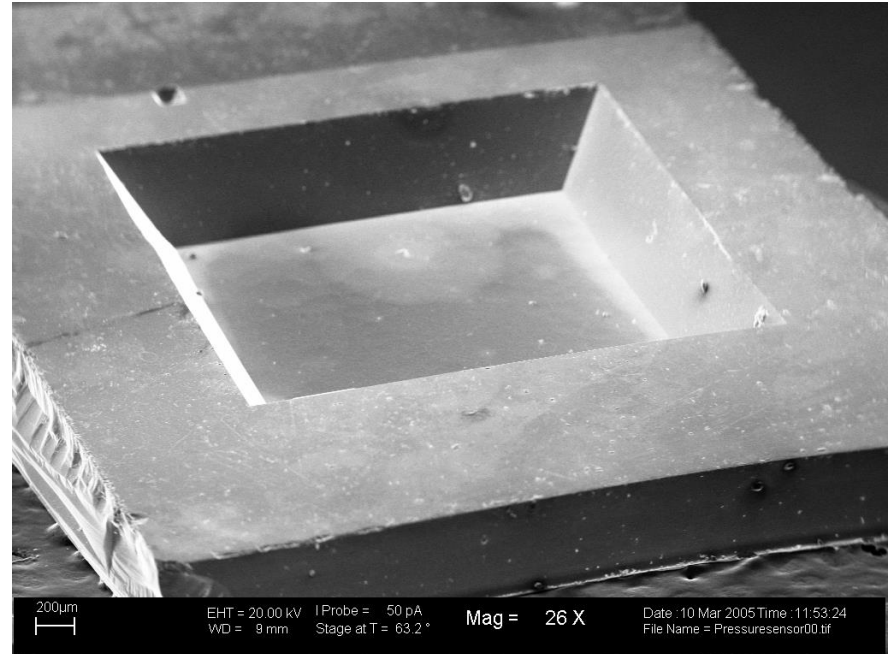
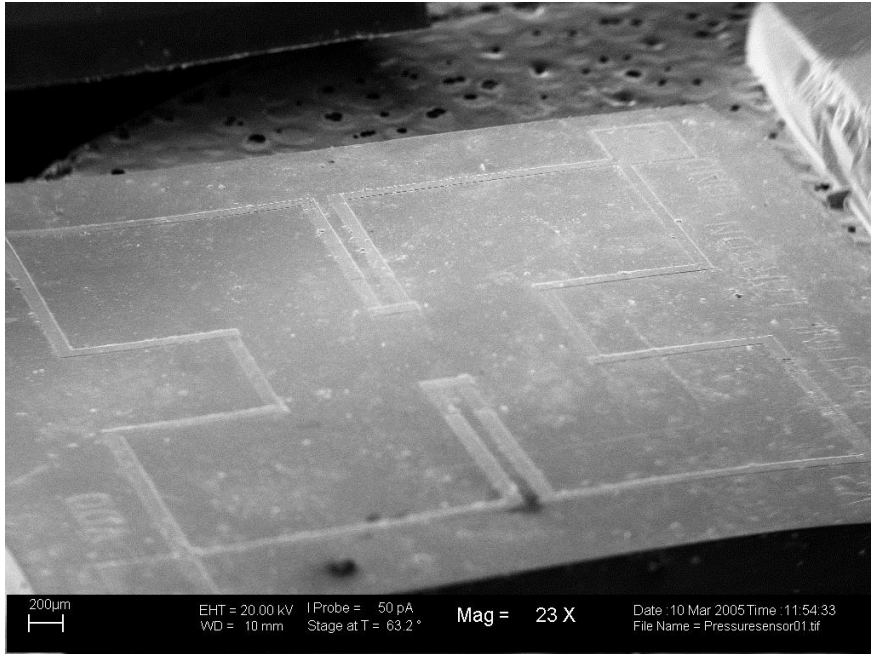




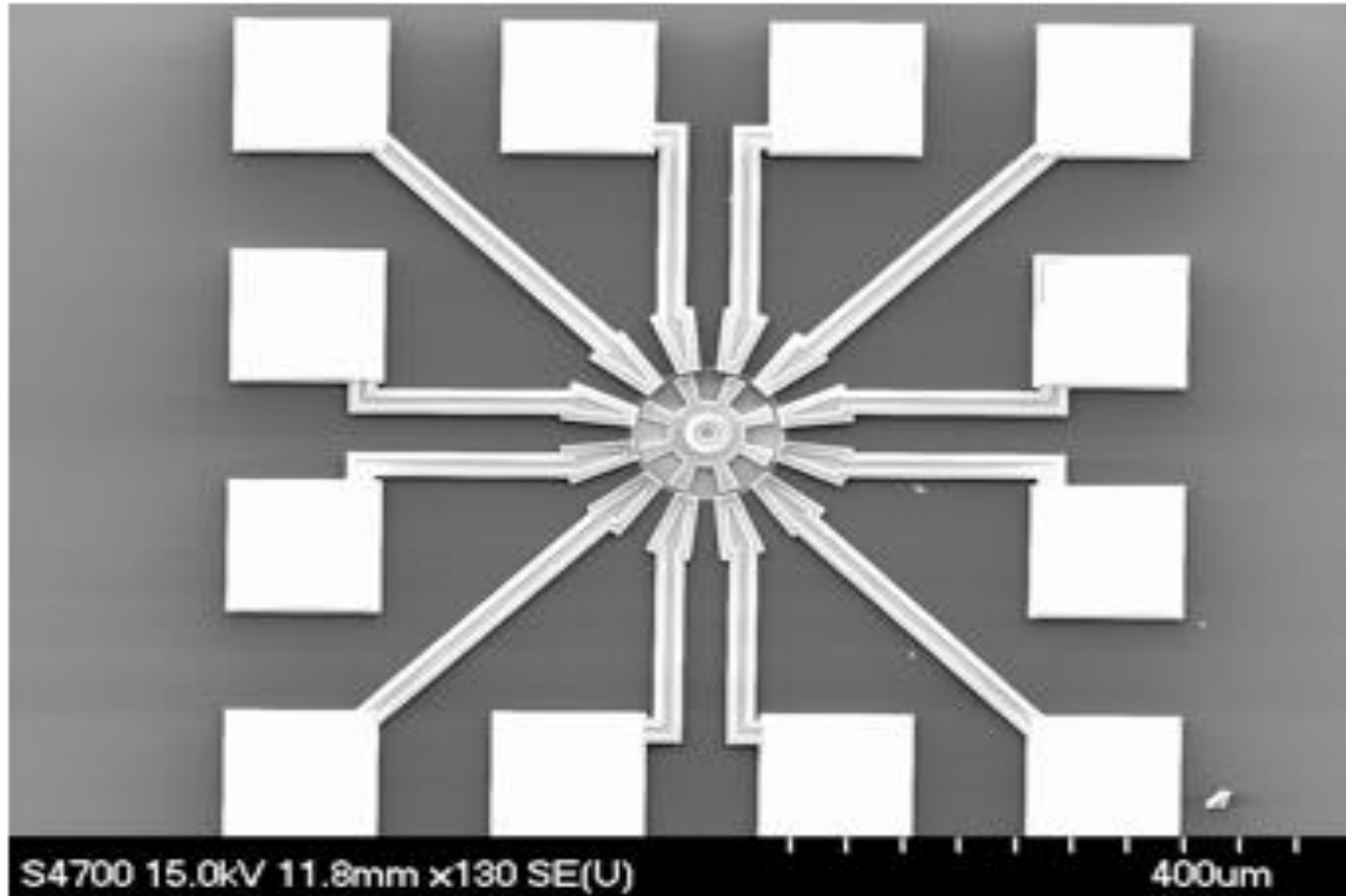
**FULE INJECTOR**



***PRESSURE SENSOR***

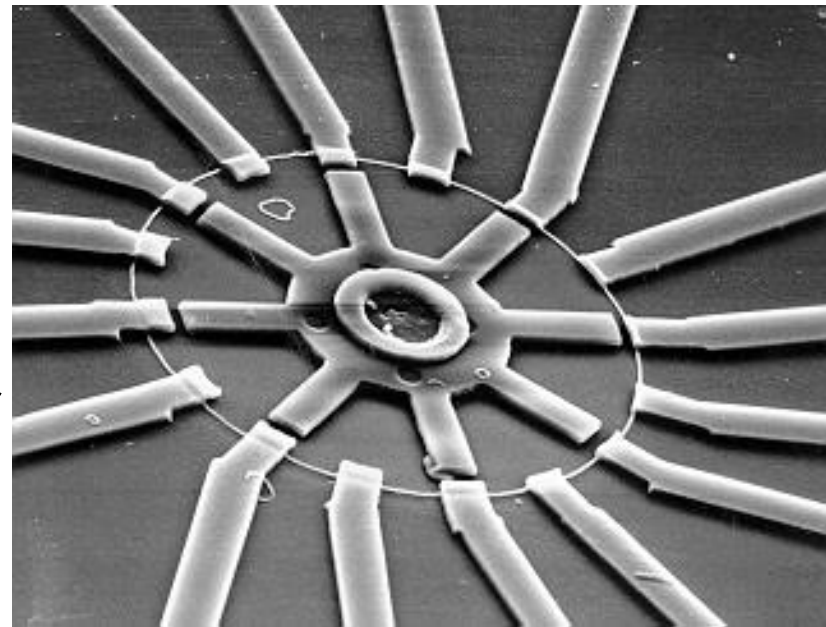
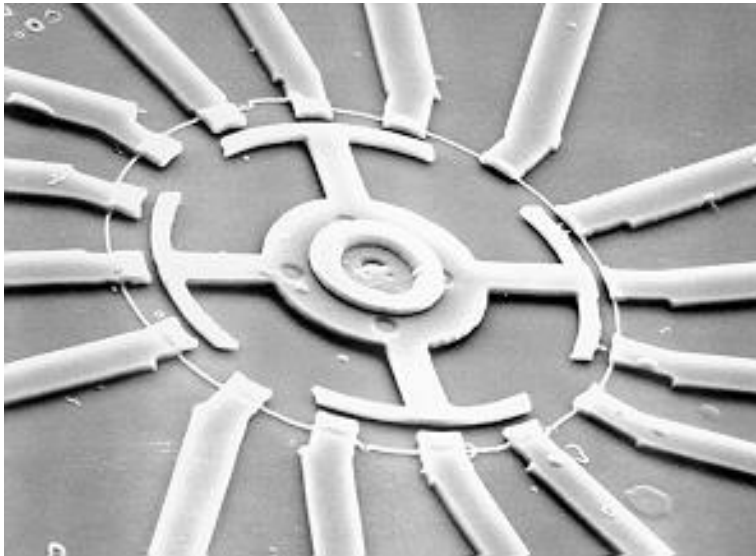


*MICROMOTOR*



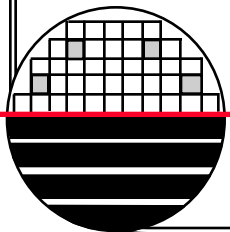
*MICROMOTORS*

100  $\mu\text{m}$

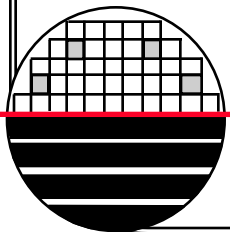
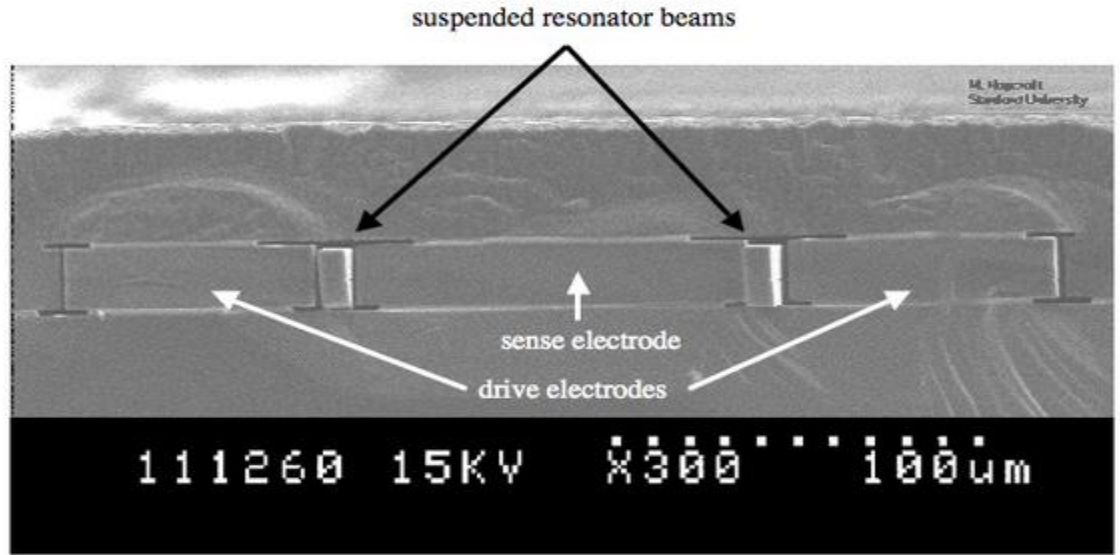
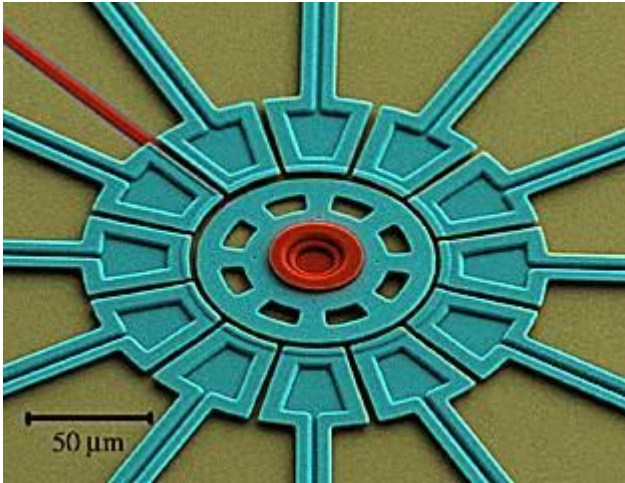


**Matt Matessa, 1991, now at  
Cypress Semiconductor  
San Jose, CA**

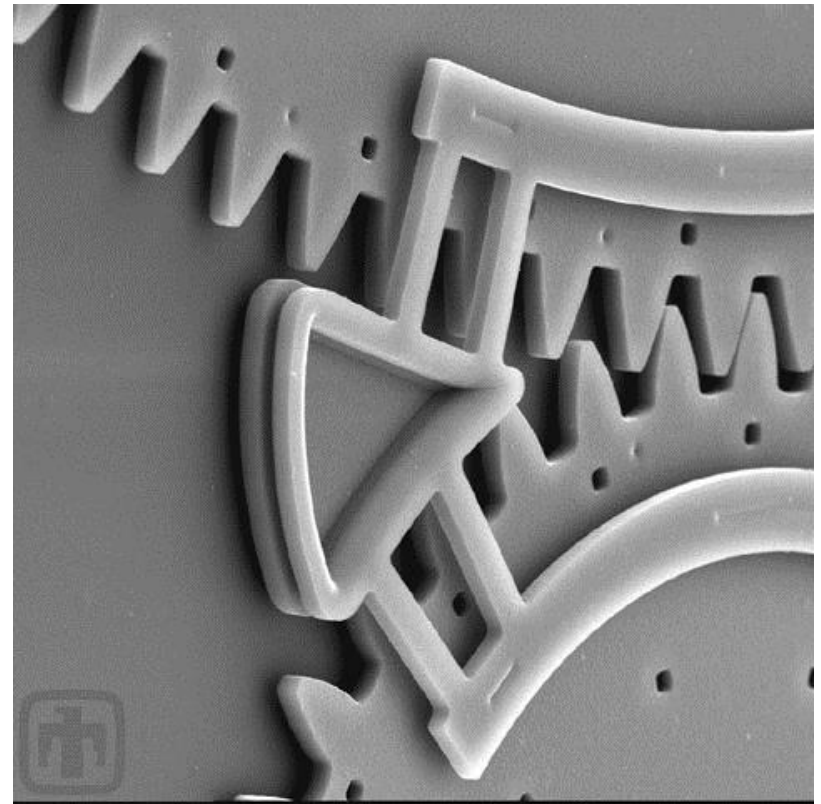
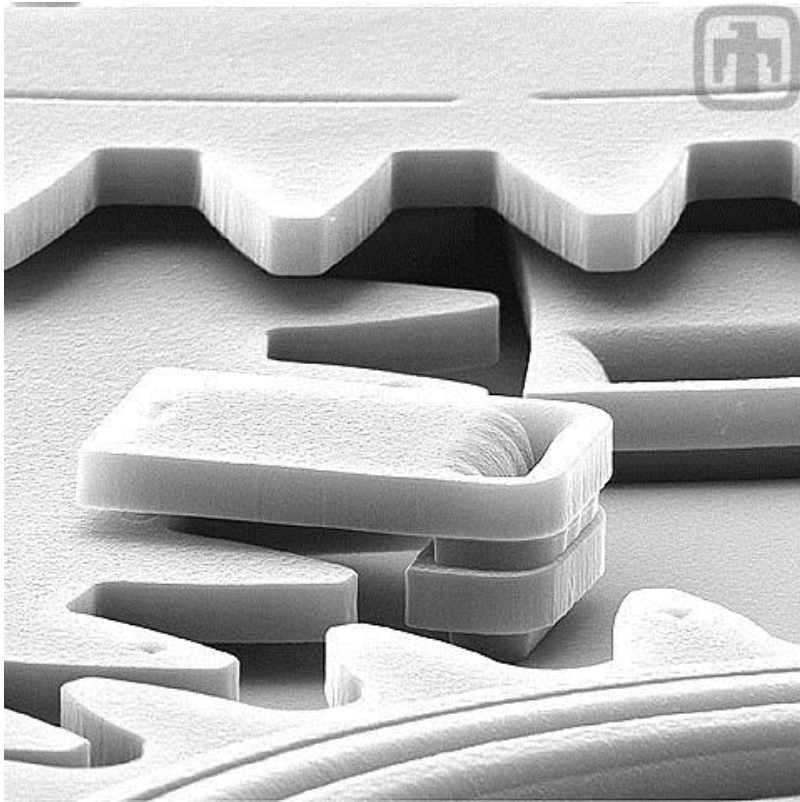
*Rochester Institute of Technology  
Microelectronic Engineering*



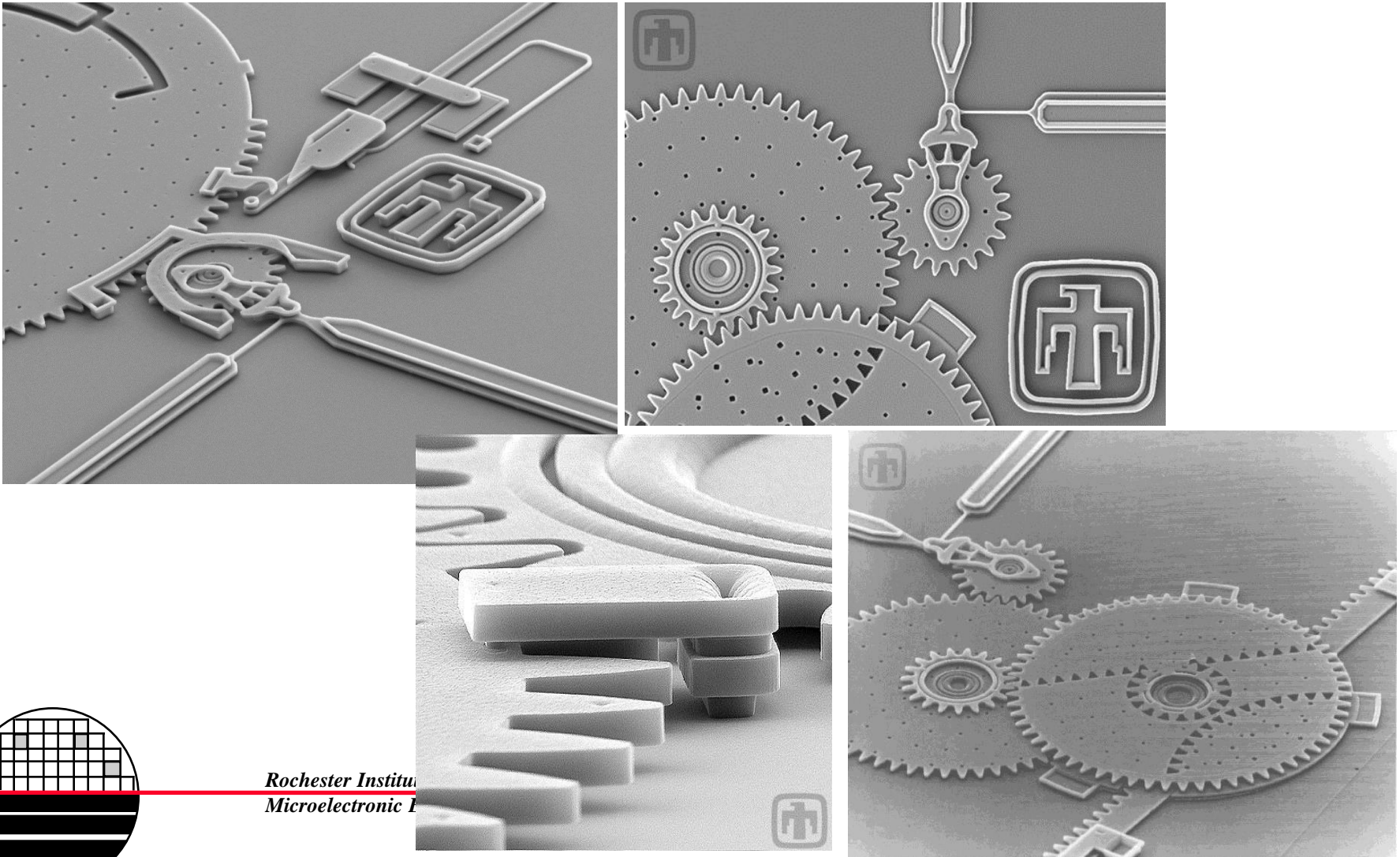
# MICRO MOTORS



*SANDIA GEARS AND LINKAGES*

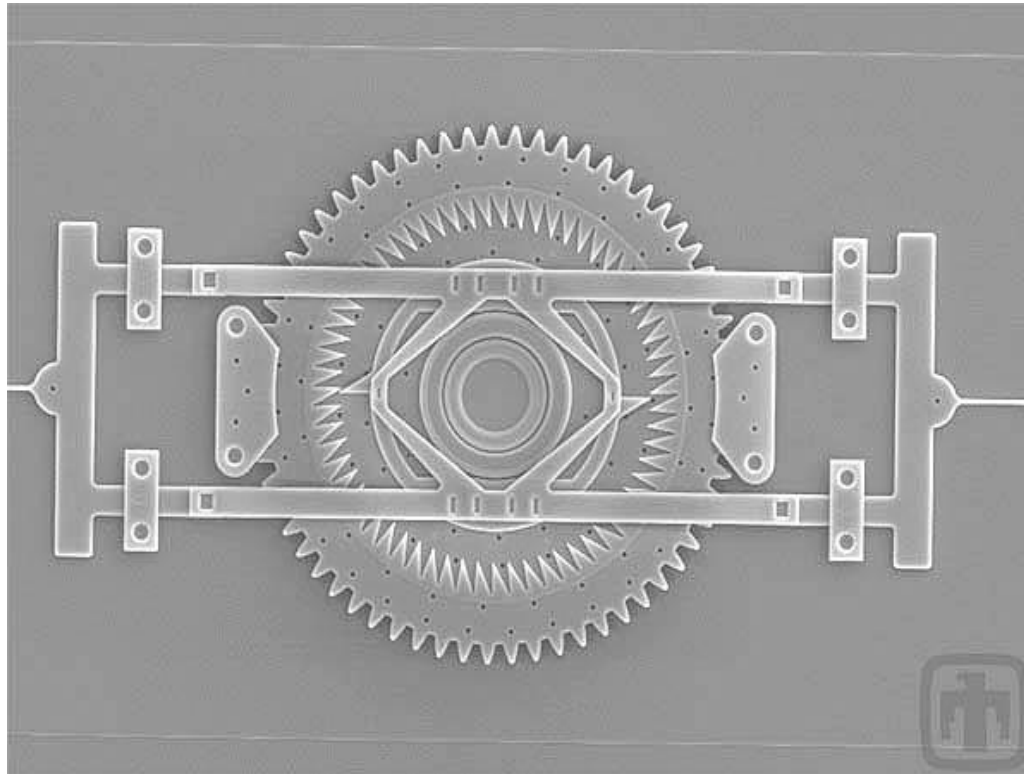


*SANDIA GEARS AND LINKAGES*



Rochester Institute  
Microelectronic E

## *INDEXING MOTOR*

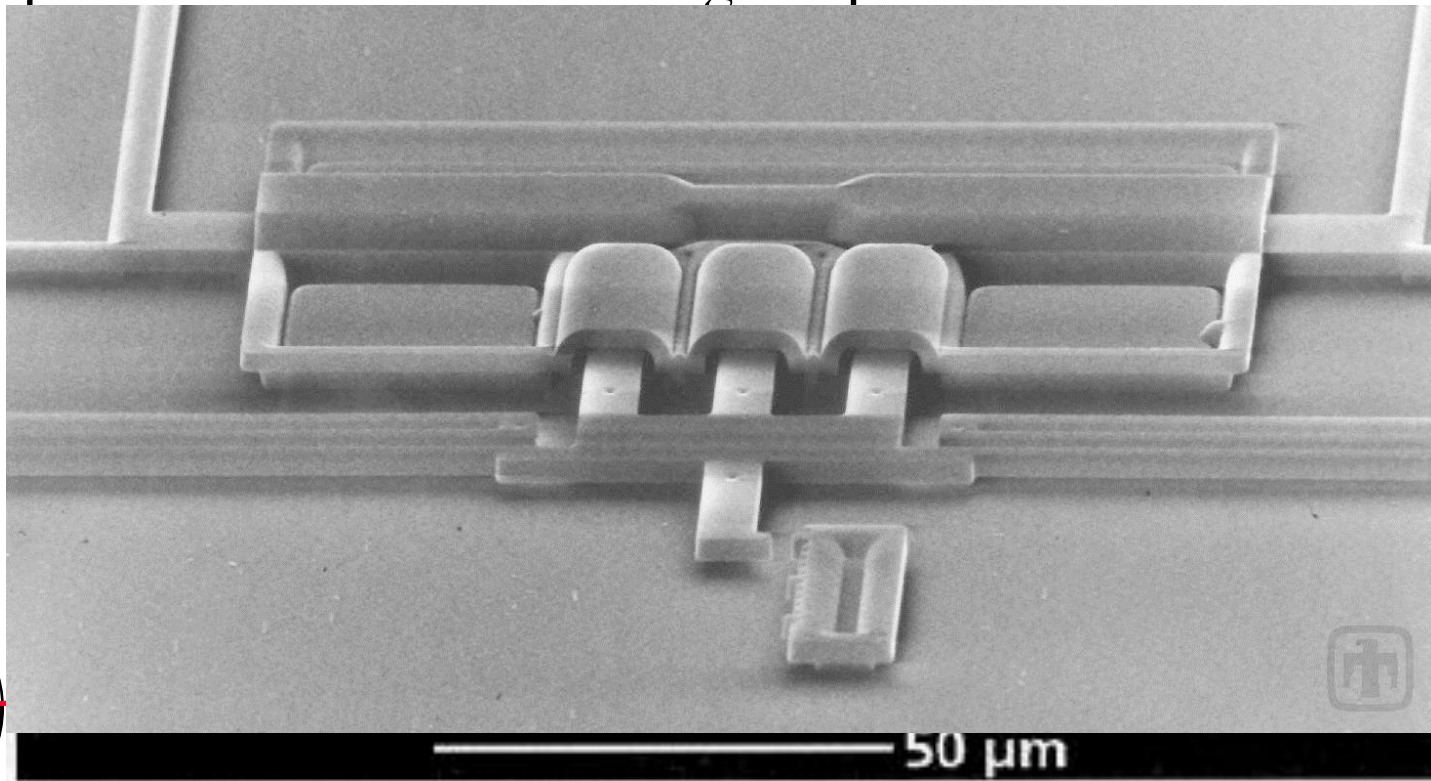


This is an indexing motor. There are two teeth that engage the gears teeth this is designed to make one step at a time. One of the indexing (inside) teeth are meshed with the gear at all times [http://mems.sandia.gov/gallery/images\\_indexing\\_motors.html](http://mems.sandia.gov/gallery/images_indexing_motors.html)



***SANDIA STEAM ENGINE***

The above device is a single-piston steam engine fabricated by Sandia National Labs. A small amount of water is heated as a current passes through the device. The water vaporizes and pushes on the piston. After the current is removed, the capillary forces inside the cylinder pull the piston back down to its original position.



# MIRROR

<http://www.bacteria-world.com/mems-mirror.htm>

## MEMS Mirror

### Optical Window and Lens

www.yooptics.com

Germanium, Silicon, MgF2, CaF2, Sapphire Window and Lens



AdChoices

### This Site:

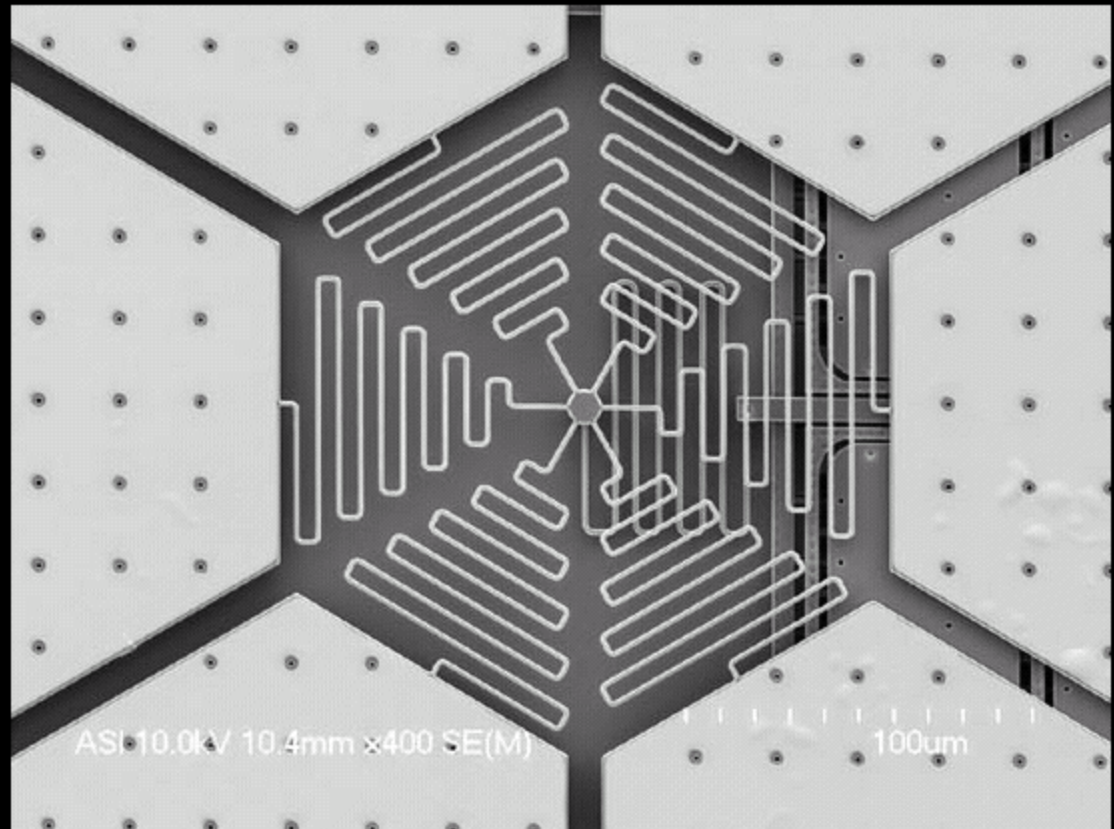
- Home
- Bacteria Pictures
- Biofilms
- Blood Cells
- Links
- Contact Us

AdChoices

### MEMS Fabrication

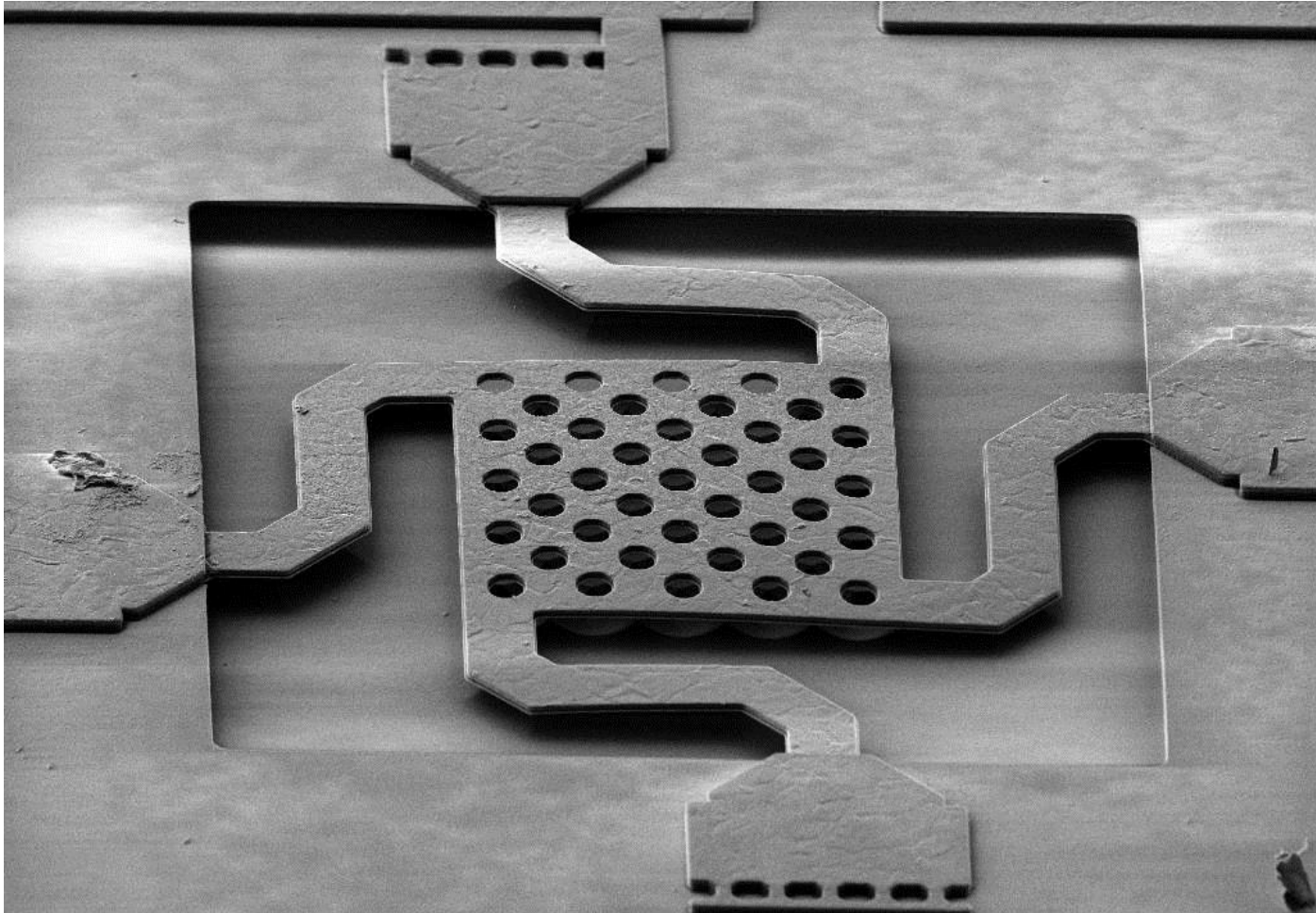
www.roguevalleymicro.com

Quality MEMS



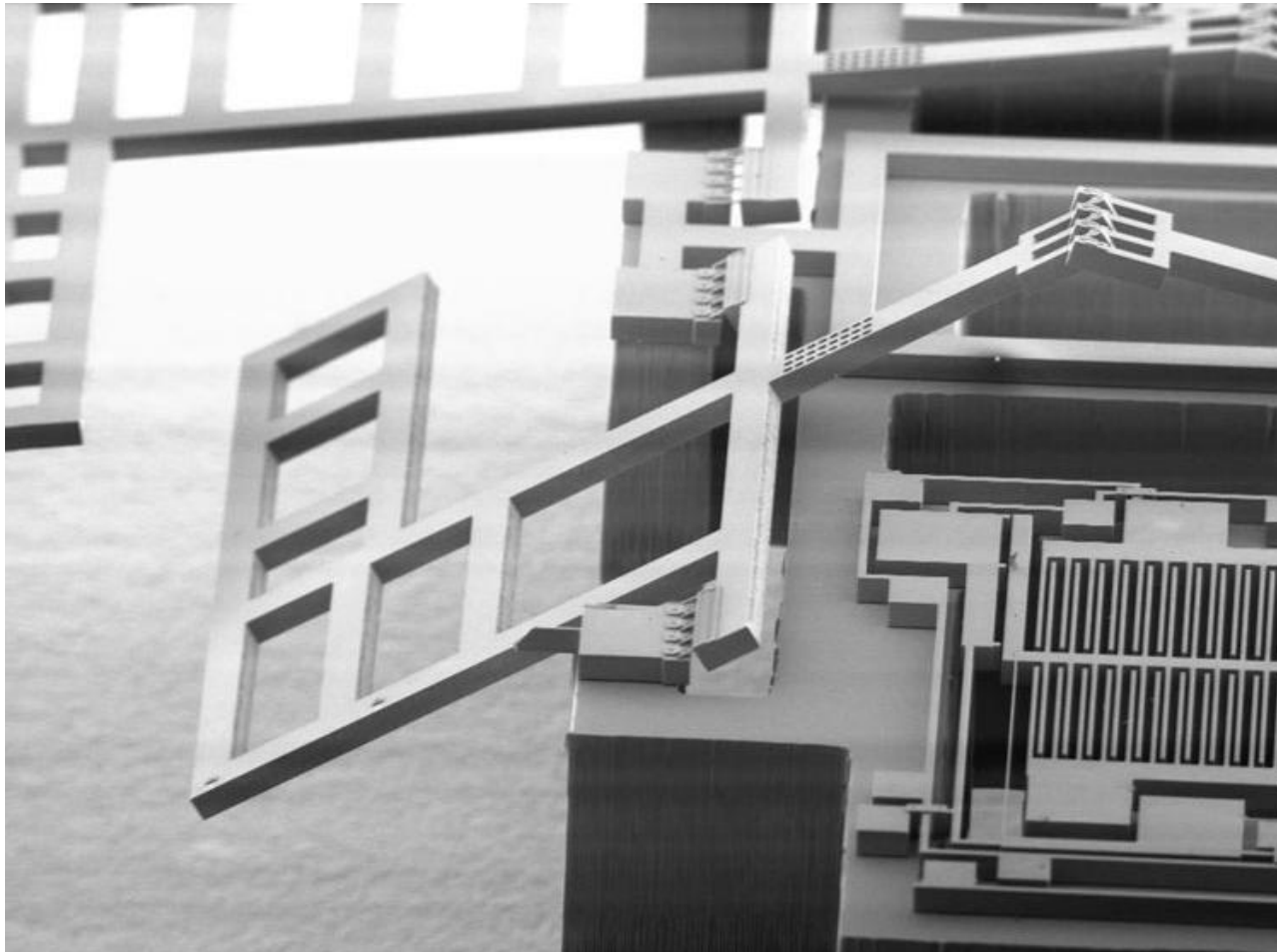
MEMS Mirror

*SUSPENDED PLATFORM*



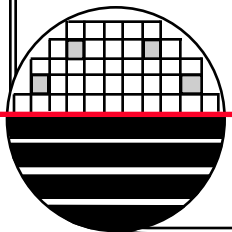
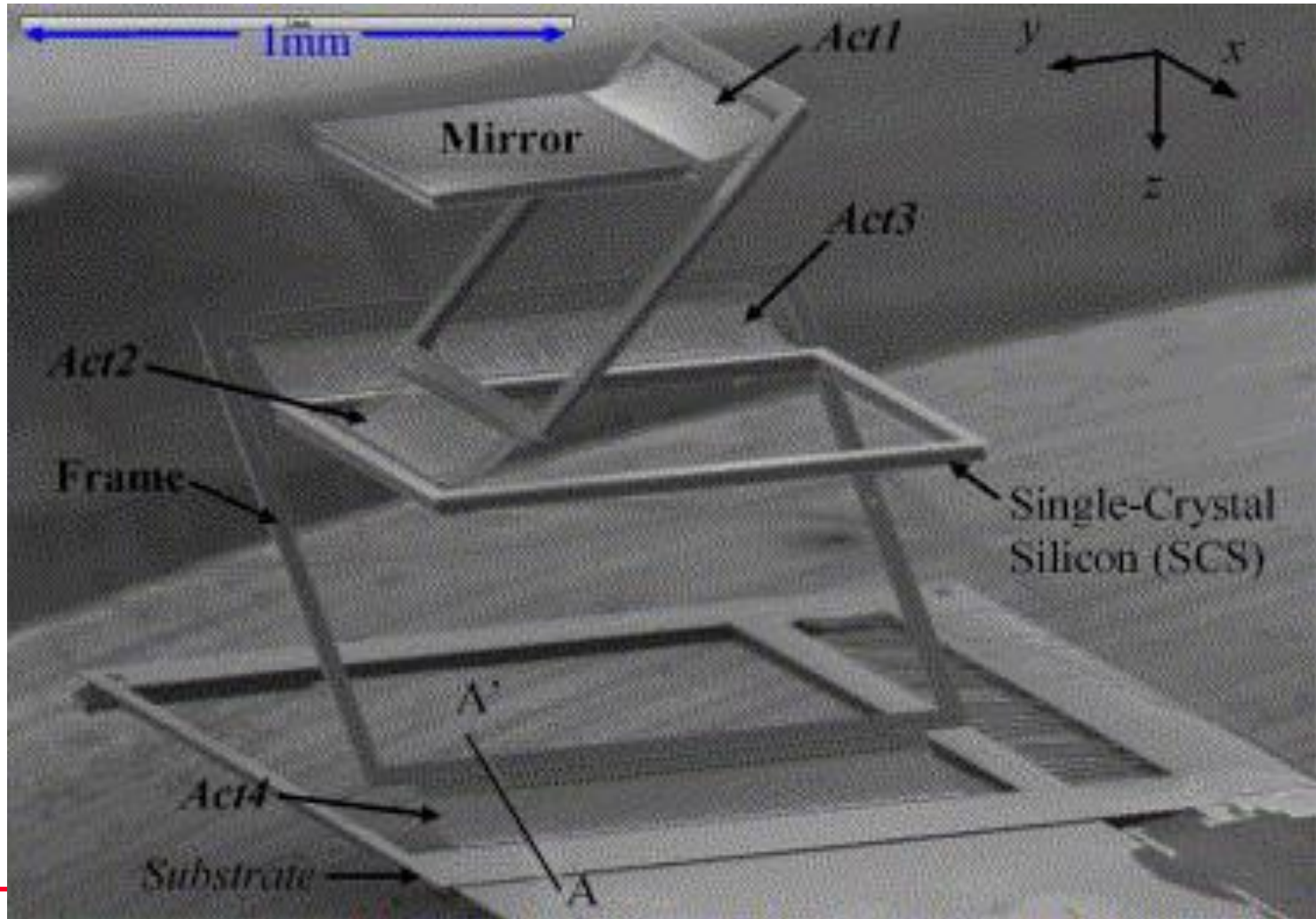
Mag = 2.00 K X      10 µm      Aperture No. = 1      EHT = 3.00 kV      Signal A = SE2      Date :25 Jul 2008      Time :13:09:00  
FIB Lock Mags = No      Aperture Size = 30.00 µm      WD = 5.0 mm      FIB Probe = 30KV:500 pA      FIB Imaging = SEM      CNM-IMB & ICN

# *HINDGES*

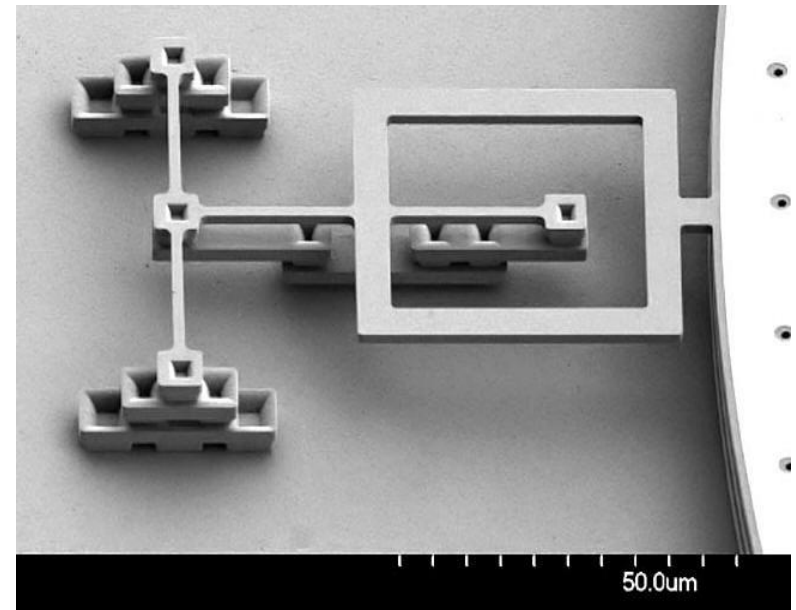
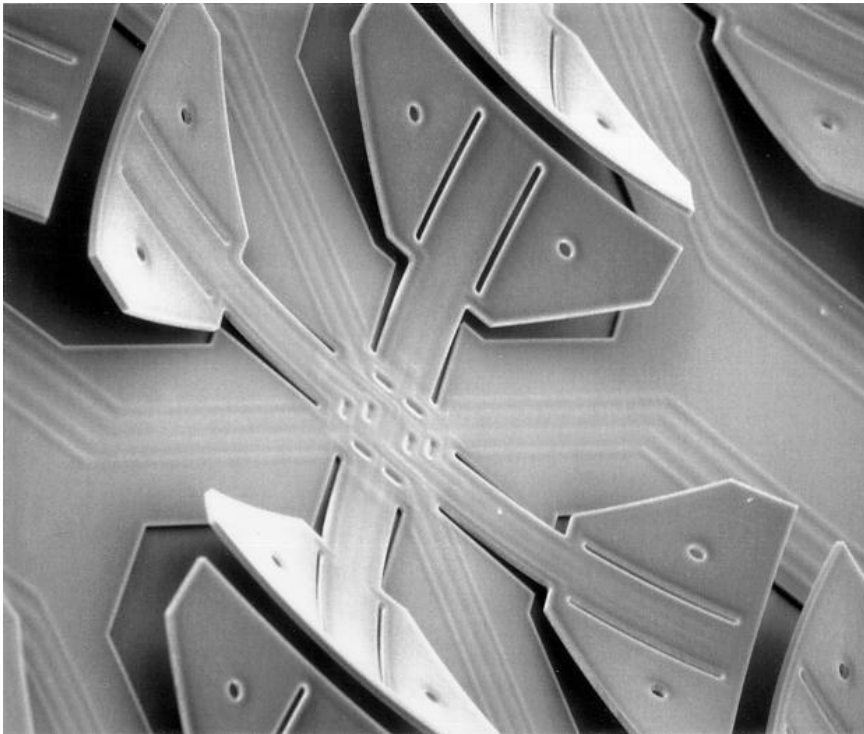


<http://coe.berkeley.edu/labnotes/0903/pister.html>

# ELECTROTHERMAL ACTUATORS

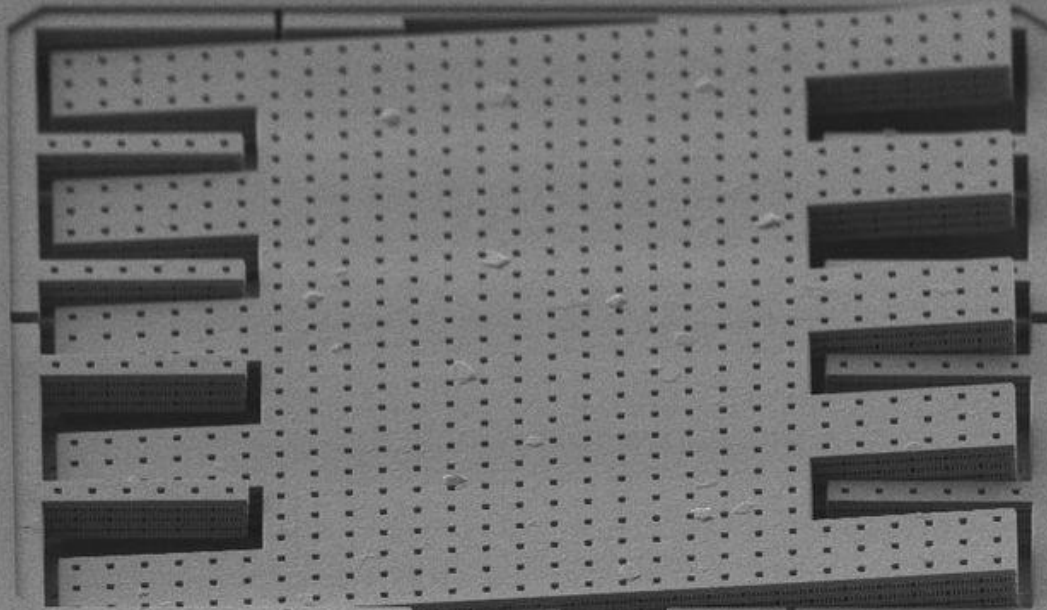


*INTERESTING STRUCTURES*



*INTERESTING STRUCTURES*

System Vacuum = 6.02e-007 mbar  
FIB Gun Pressure = 3.08e-008 mbar  
Gun Vacuum = 1.13e-009 mbar



10  $\mu$ m

Mag = 1.89 K X  
WD = 5.5 mm  
EHT = 2.00 kV

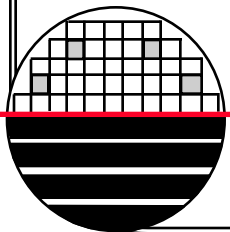
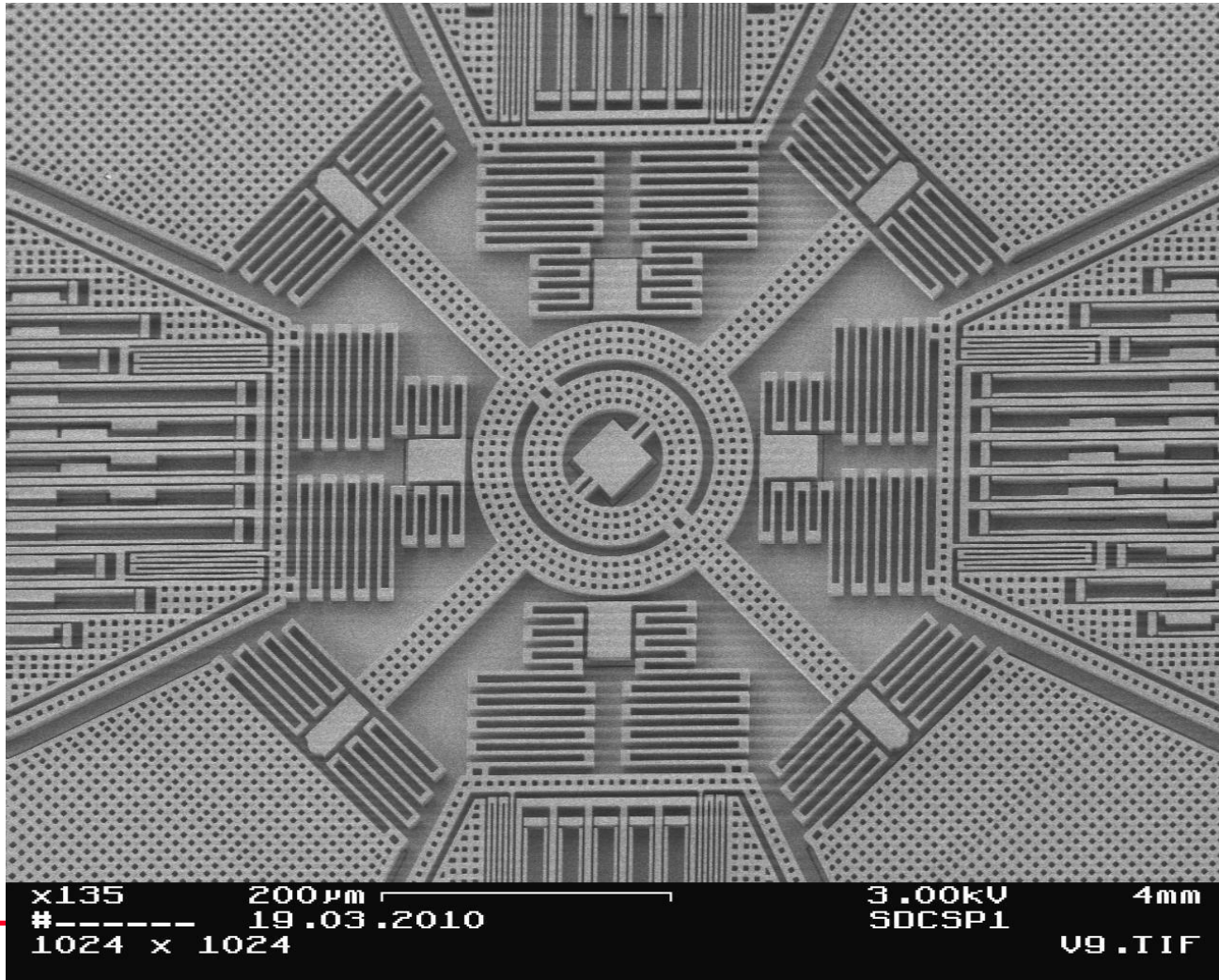
Signal A = SE2  
Tilt Corr. = Off 54.0°  
Stage at T = 54.0°

FIB Lock Mags = No  
FIB Probe = 30KV:1 pA  
FIB Imaging = SEM

Date : 18 Feb 2010  
Time : 13:31:53

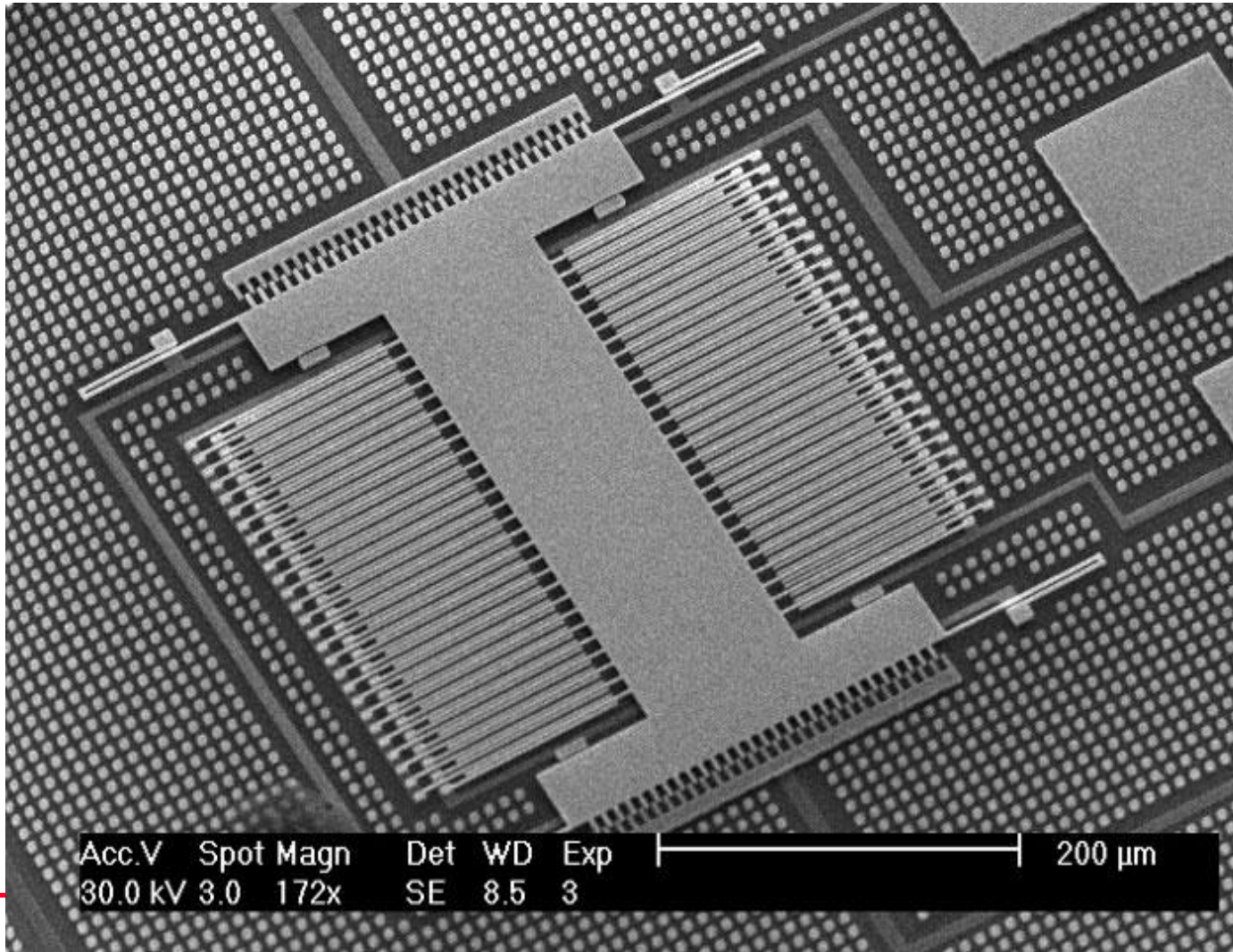


*INTERESTING STRUCTURES*

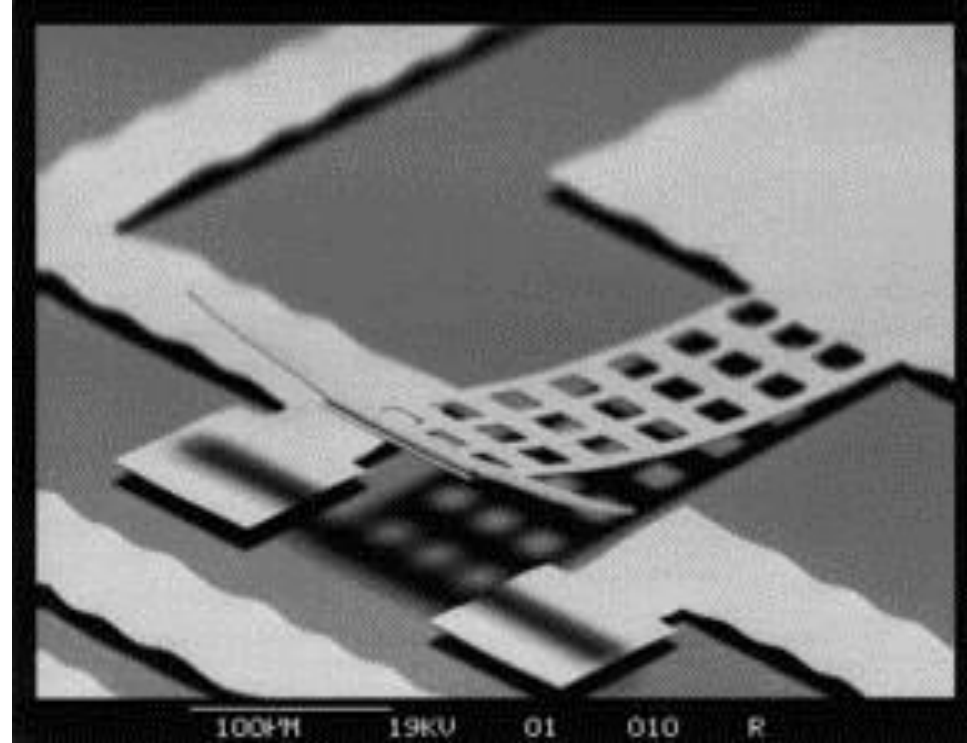
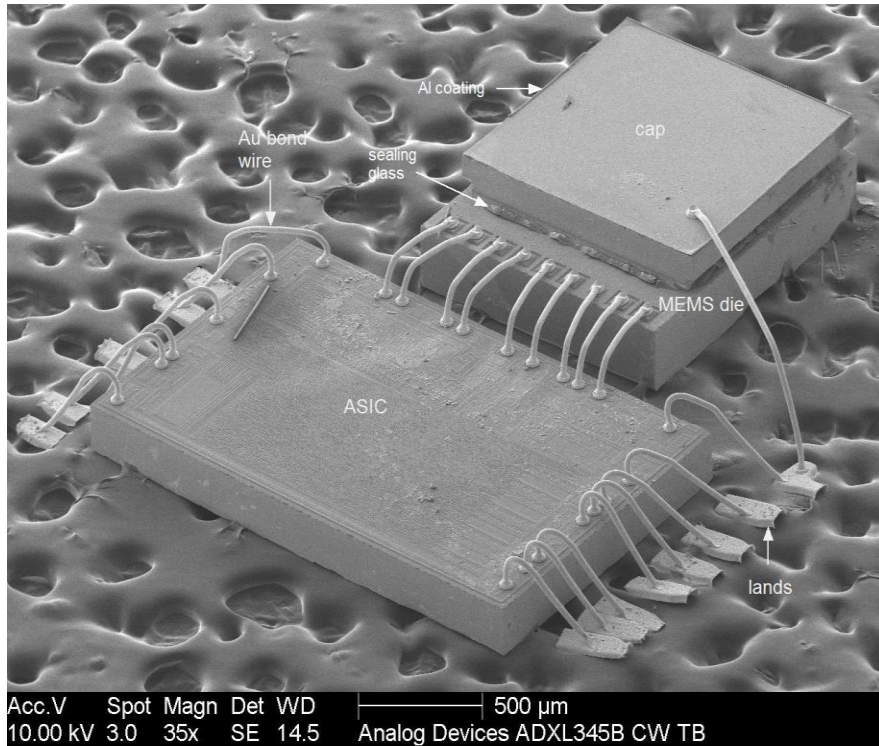




*INTERESTING STRUCTURES*

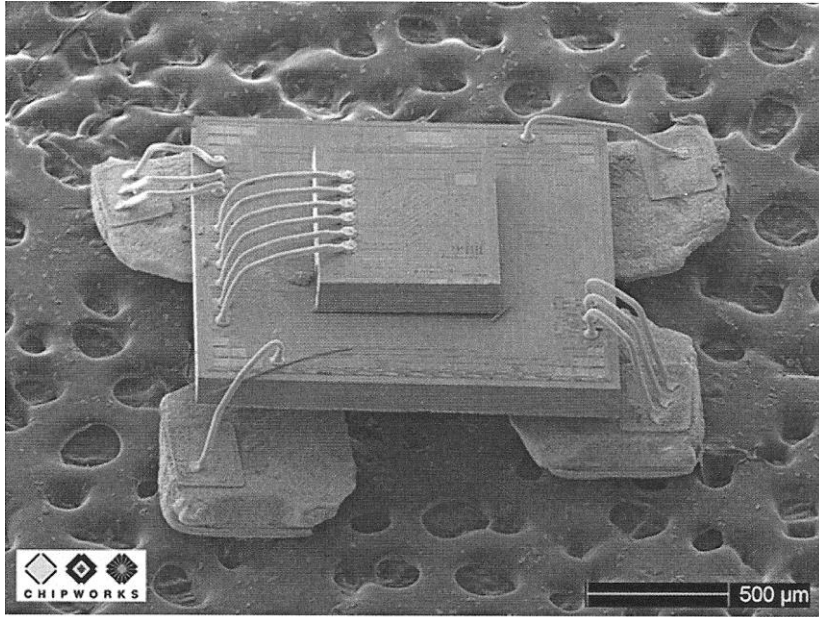


**MULTI CHIP IN SINGLE PACKAGE & MEMS SWITCH**

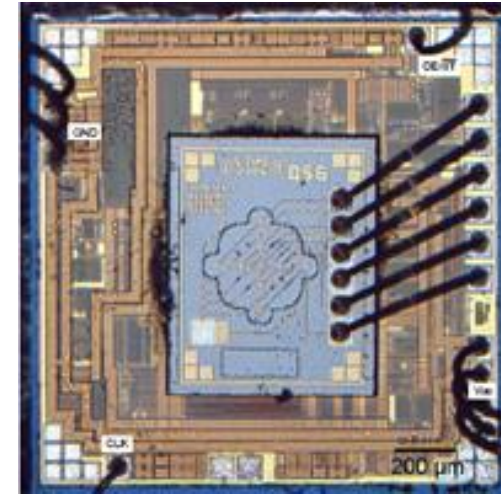


3-axis accelerometer

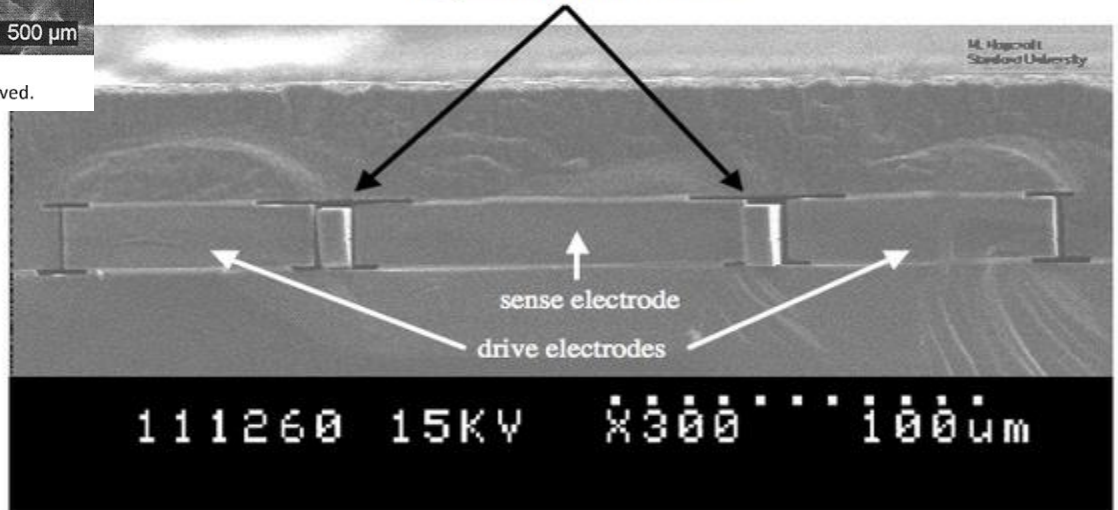
# SiTime Oscillator



Above is a picture of the SiTime S18002AC package with its outer protective casing removed.

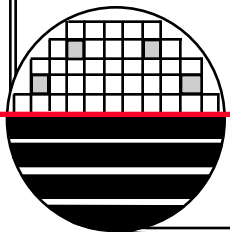


suspended resonator beams



## REFERENCES

1. Microsensors, Edited by Richard S. Muller, Roger T. Howe, Stephen d. Senturia, Rosemary L. Smith, Richard M. White, IEEE Press, 1990, ISBN 0-87942-245-9
2. Silicon Sensors and Microstructures, Janusz Brysek, Kurt Petersen, Joseph Mallon, Lee Christel, Farzad Pourahmadi, 1990 Nova Sensor, 1055 Mission Court, Fremont, CA 94539, (415)490-9100
3. <http://www.mdl.sandia.gov>
4. <http://www-mtl.mit.edu/semisubway.html>
5. [Joel%20SEM%20guide.pdf](#)



***HOMEWORK – MEM SEMS***

1. Go online and find a high quality SEM picture of a MEMS device. (other than the ones in this presentation)
2. Write a brief description of the device.
3. Email an electronic copy to Dr. Fuller

